

Chapter 3

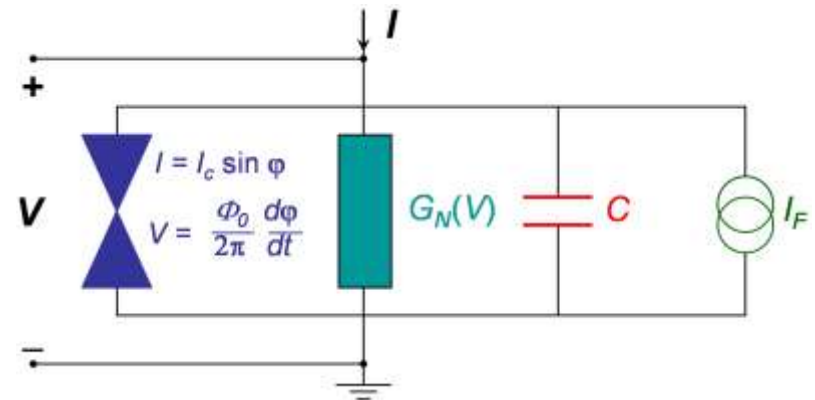
Physics of Josephson Junctions:

The Voltage State

3. Physics of Josephson junctions: The voltage state

For bias currents $I > I_S^m$

- Finite junction voltage
- Phase difference φ evolves in time: $\frac{d\varphi}{dt} \propto V$
- Finite voltage state of the junction corresponds to a **dynamic state**
- Only part of the total current is carried by the Josephson current
 - additional **resistive channel**
 - **capacitive channel**
 - noise channel



Key questions

- How does the phase dynamics look like?
- Current-voltage characteristics for $I > I_S^m$?
- What is the influence of the resistive damping ?

3.1 The basic equation of the lumped Josephson junction

3.1.1 The normal current: Junction resistance

At finite temperature $T > 0$

→ Finite density of “normal” electrons

→ **Quasiparticles**

→ Zero-voltage state: No quasiparticle current

→ For $V > 0$ → Quasiparticle current = Normal current I_N → **Resistive state**

High temperatures close to T_c

→ For $T \lesssim T_c$ and $2\Delta(T) \ll k_B T$: (almost) all Cooper pairs are broken up

→ **Ohmic current-voltage characteristic (IVC)**

→ $I_N = G_N V$, where $G_N \equiv \frac{1}{R_N}$ is the **normal conductance**

Large voltage $V > V_g = \frac{\Delta_1 + \Delta_2}{e}$

→ External circuit provides energy to break up Cooper pairs

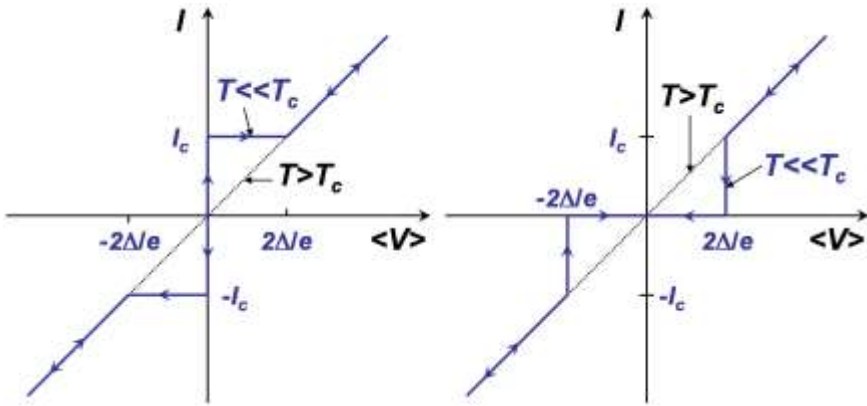
→ **Ohmic IVC**

For $T \ll T_c$ and $|V| < V_g$

→ Vanishing quasiparticle density → No normal current

3.1.1 The normal current: Junction resistance

Current-voltage characteristic



For $T \ll T_c$ and $|V| < V_g$

→ IVC depends on sweep direction and on bias type (current/voltage)

→ **Hysteretic behavior**

→ Current bias → $I = I_s + I_N = const.$

Equivalent conductance G_N at $T = 0$:

$$G_N(V) = \begin{cases} 0 & \text{for } |V| < 2\Delta/e \\ \frac{1}{R_N} & \text{for } |V| \geq 2\Delta/e \end{cases}$$

Voltage state

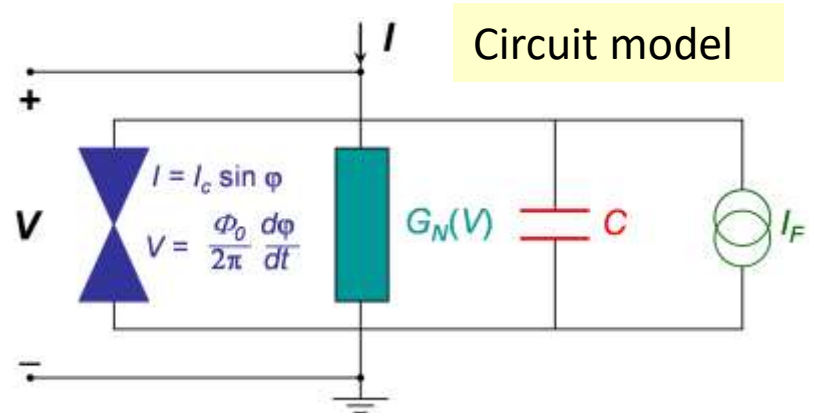
→ Bias current I

→ $I_s(t) = I_c \sin \varphi(t)$ is time dependent

→ I_N is time dependent

→ Junction voltage $V = \frac{I_N}{G_N}$ is time dependent

→ IVC shows **time-averaged voltage** $\langle V \rangle$



3.1.1 The normal current: Junction resistance

Finite temperature

→ **Sub-gap resistance** $R_{sg}(T)$ for $|V| < V_g$

→ $R_{sg}(T)$ determined by amount of thermally excited quasiparticles

$$G_{sg}(T) = \frac{1}{R_{sg}(T)} = \frac{n(T)}{n_{tot}} G_N \quad n(T) \rightarrow \text{Density of excited quasiparticles}$$

→ for $T > 0$ we get

$$G_N(V, T) = \begin{cases} \frac{1}{R_{sg}(T)} & \text{for } |V| < 2\Delta(T)/e \\ \frac{1}{R_N} & \text{for } |V| \geq 2\Delta(T)/e \end{cases} \quad \rightarrow \text{Nonlinear conductance } G_N(V, T)$$

→ Characteristic voltage (**$I_c R_N$ -product**)

$$V_c \equiv I_c R_N = \frac{I_c}{G_N}$$

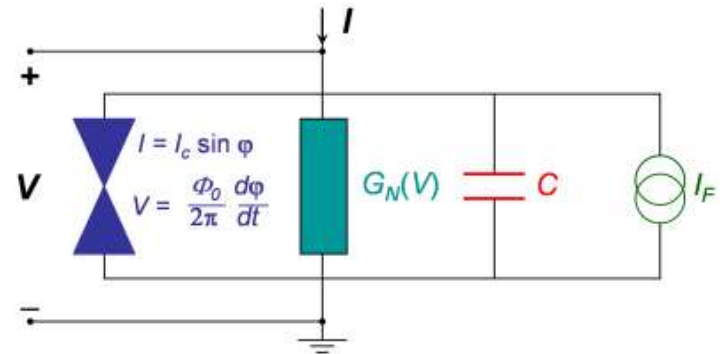
Note: → There may be a frequency dependence of the normal channel
→ Normal channel depends on junction type

3.1.2 The displacement current: Junction capacitance

If $\frac{dV}{dt} \neq 0 \rightarrow$ Finite **displacement current** $I_D = C \frac{dV}{dt}$

$\rightarrow C \leftrightarrow$ junction capacitance

\rightarrow For planar tunnel junction $C = \frac{\epsilon\epsilon_0 A_j}{d}$



\rightarrow Compare current values of different channels

With $V = L_c \frac{dI_s}{dt}$, $I_N = VG_N$, $I_D = C \frac{dV}{dt}$, $L_s = \frac{L_c}{\cos \varphi} \geq L_c$ and $G_N(V, T) = \frac{1}{R_N}$

$$L_c = \frac{\hbar}{2eI_c} \quad \text{Josephson inductance}$$

$$I_s \leq \frac{V}{\omega L_c} \quad I_N \leq \frac{V}{R_N} \quad I_D \simeq \omega C V$$

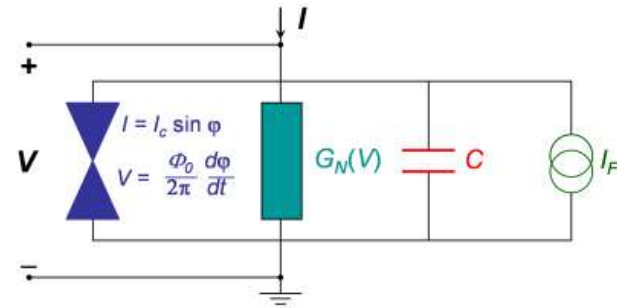
3.1.3 Characteristic times and frequencies

Characteristic frequencies

Equivalent parallel *LRC* circuit

→ L_C, R_N, C

→ Three characteristic frequencies



Plasma frequency

$$\omega_p = \frac{1}{\tau_p} \equiv \frac{1}{\sqrt{L_C C}} = \sqrt{\frac{2eI_c}{\hbar C}}$$

→ $\omega_p \propto \sqrt{\frac{J_c}{C_A}}$, where $C_A \equiv \frac{C}{A}$ is the specific junction capacitance

→ $\omega < \omega_p \rightarrow I_D < I_S$

Inductive L_C/R_N time constant

$$\omega_c = \frac{1}{\tau_c} \equiv \frac{R_N}{L_C} = \frac{2e}{\hbar} V_c = \frac{2\pi}{\Phi_0} V_c$$

$$V_c = I_c R_N$$

→ Inverse relaxation time in the normal+supercurrent system

→ ω_c follows from V_c (2nd Josephson equation)

→ ω_c - characteristic frequency

→ $I_N < I_c$ for $V < V_c$ or $\omega < \omega_c$

Capacitive $R_N C$ time constant

$$\omega_{RC} = \frac{1}{\tau_{RC}} \equiv \frac{1}{R_N C} = \frac{\omega_p^2}{\omega_c}$$

→ $I_D < I_N$ for $\omega < \frac{1}{\tau_{RC}}$

3.1.3 Characteristic times and frequencies

Stewart-McCumber parameter and quality factor

→ Stewart-McCumber parameter $\beta_C \equiv \frac{\omega_c^2}{\omega_p^2} = \frac{\omega_c}{\omega_{RC}} = \omega_c \tau_{RC} = \frac{2e}{\hbar} I_c R_N^2 C$

→ Quality factor $Q = \frac{RC}{\sqrt{LC}} = \frac{\omega_p}{\omega_{RC}} = \frac{\omega_c}{\omega_p} = \sqrt{\beta_C}$

(Q compares the decay of oscillation amplitudes to the oscillation period)

Limiting cases

→ $\beta_C \ll 1$

- Small capacitance and/or small resistance
- Small $R_N C$ time constants ($\tau_{RC} \omega_p \ll 1$)
- Highly damped (**overdamped**) junctions

→ $\beta_C \gg 1$

- Large capacitance and/or large resistance
- Large $R_N C$ time constants ($\tau_{RC} \omega_p \gg 1$)
- Weakly damped (**underdamped**) junctions

3.1.4 The fluctuation current

Fluctuation/noise

- **Langevin** method: include **random source** → fluctuating noise current
- type of fluctuations: **thermal noise, shot noise, 1/f noise**

Thermal Noise

Johnson-Nyquist formula for thermal noise ($k_B T \gg eV, \hbar\omega$):

$$S_I(f) = \frac{4k_B T}{R_N} \quad (\text{current noise power spectral density})$$

$$S_V(f) = 4k_B T R_N \quad (\text{voltage noise power spectral density})$$

relative noise intensity (thermal energy/Josephson coupling energy):

$$\gamma \equiv \frac{k_B T}{E_J} = \frac{2e k_B T}{\hbar I_c} \quad \Rightarrow \quad \gamma \equiv \frac{I_T}{I_c} \quad \text{with} \quad I_T = \frac{2e}{\hbar} k_B T$$

$I_T \equiv$ thermal noise current

$T = 4.2 \text{ K} \rightarrow I_T \approx 0.15 \text{ } \mu\text{A}$

3.1.4 The fluctuation current

Shot Noise

Schottky formula for shot noise ($eV \gg k_B T \rightarrow V > 0.5 \text{ mV @ } 4.2 \text{ K}$): $S_I(f) = 2eI_N$

- Random fluctuations due to the discreteness of charge carriers
- Poisson process → **Poissonian distribution**
- Strength of fluctuations → variance $\Delta I^2 \equiv \langle (I - \langle I \rangle)^2 \rangle$
- Variance depends on frequency → Use noise power:

$$S(f) = \int_{-\infty}^{+\infty} (\langle I(t)I(0) \rangle - \langle I(0) \rangle^2) dt$$

includes equilibrium fluctuations (white noise)

1/f noise

- Dominant at **low frequencies**
- Physical nature often unclear
- Josephson junctions: **dominant below about 1 Hz - 1 kHz** → Not considered here

3.1.5 The basic junction equation

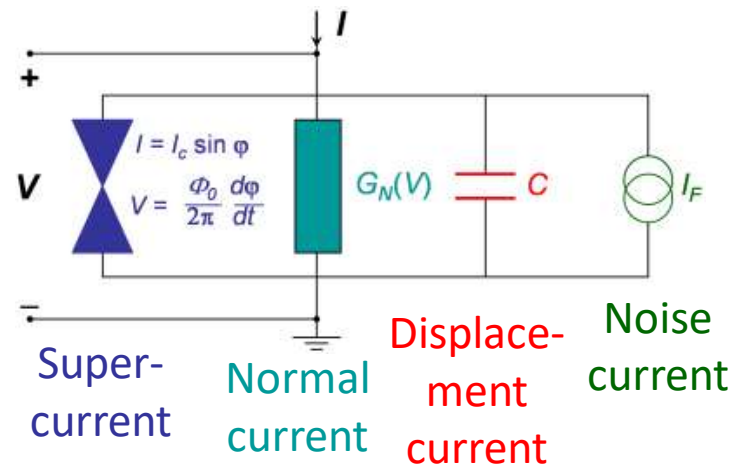
Kirchhoff's law:

$$I = I_S + I_N + I_D + I_F$$

Voltage-phase relation:

$$\frac{d\varphi}{dt} = \frac{2eV}{\hbar}$$

→ Basic equation of a Josephson junction



$$\Rightarrow I = I_c \sin \varphi + G_N(V)V + C \frac{dV}{dt} + I_F$$

$$\Rightarrow I = I_c \sin \varphi + G_N(V) \frac{\Phi_0}{2\pi} \frac{d\varphi}{dt} + C \frac{\Phi_0}{2\pi} \frac{d^2\varphi}{dt^2} + I_F$$

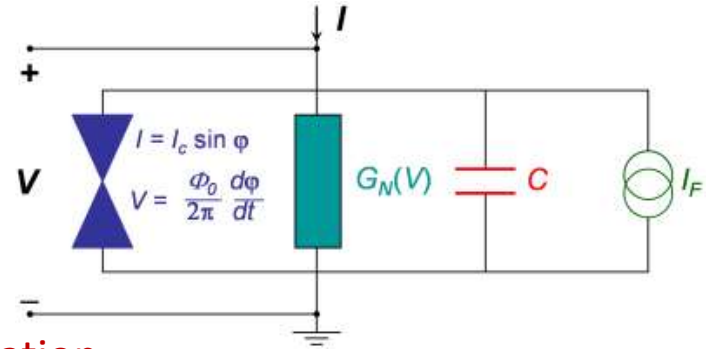
Nonlinear differential equation with nonlinear coefficients

- Complex behavior, numerical solution
- Use approximations (simple models)

3.2 The resistively and capacitively shunted junction (RCSJ) model

Resistively and Capacitively Shunted Junction (RCSJ) model

Approximation $\rightarrow G_N(V) \equiv G = R^{-1} = \text{const.}$
 $R = \text{Junction normal resistance}$



Differential equation in dimensionless or **energy formulation**

$$\left(\frac{\hbar}{2e}\right) C \frac{d^2\varphi}{dt^2} + \left(\frac{\hbar}{2e}\right) \frac{1}{R} \frac{d\varphi}{dt} + I_c \left[\sin\varphi - \frac{I}{I_c} + \frac{I_F(t)}{I_c} \right] = 0$$

$$\Rightarrow \left(\frac{\hbar}{2e}\right)^2 C \frac{d^2\varphi}{dt^2} + \left(\frac{\hbar}{2e}\right)^2 \frac{1}{R} \frac{d\varphi}{dt} + \frac{d}{d\varphi} \{E_{J0} [1 - \cos\varphi - i\varphi + i_F(t)\varphi]\} = 0$$

$\equiv i \quad \equiv i_F(t)$

Mechanical analog

Gauge invariant phase difference \leftrightarrow Particle with mass M and damping η in potential U :

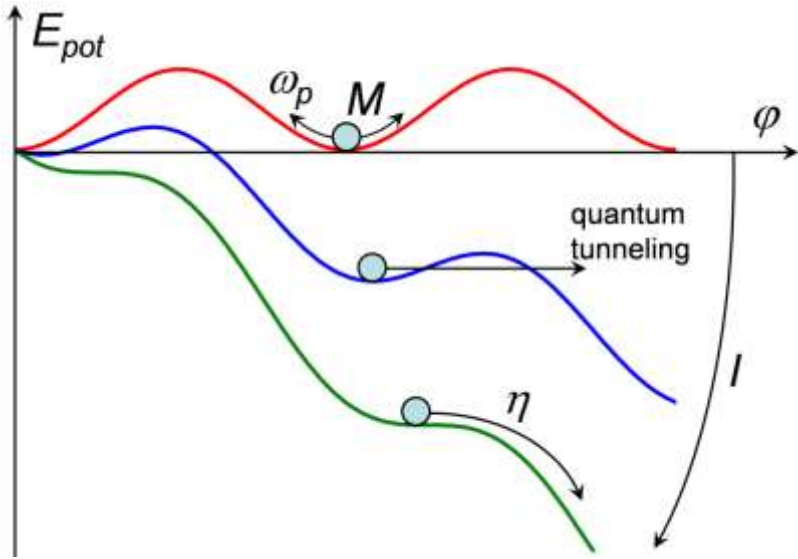
$$M \frac{d^2x}{dt^2} + \eta \frac{dx}{dt} + \nabla U = 0$$

with $M = \left(\frac{\hbar}{2e}\right)^2 C \quad \eta = \left(\frac{\hbar}{2e}\right)^2 \frac{1}{R}$

$$U = E_{J0} [1 - \cos\varphi - i\varphi + i_F(t)\varphi]$$

Tilted washboard potential

3.2 The resistively and capacitively shunted junction (RCSJ) model



Finite tunneling probability:
 → Macroscopic quantum tunneling (MQT)

Escape by thermal activation
 → Thermally activated phase slips

Normalized time: $\tau \equiv \frac{t}{\tau_c} = \frac{t}{2eI_c R / \hbar}$

Stewart-McCumber parameter: $\beta_C \equiv \frac{\omega_c^2}{\omega_p^2} = \frac{2e}{\hbar} I_c R_N^2 C$

$$\beta_C \frac{d^2\varphi}{d\tau^2} + \frac{d\varphi}{d\tau} + \sin\varphi - i - i_F(\tau) = 0$$

Motion of „phase particle“ φ in the tilted washboard potential

Plasma frequency

→ Neglect damping, zero driving and small amplitudes ($\sin\varphi \approx \varphi$)

$$\beta_C \frac{d^2\varphi}{d\tau^2} + \varphi = 0$$

Solution: $\varphi = c \cdot \exp\left(i \frac{\tau}{\sqrt{\beta_C}}\right) = c \cdot \exp\left(i \frac{t}{\sqrt{\beta_C} \tau_c}\right) = c \cdot \exp(i\omega_p t)$

Plasma frequency = Oscillation frequency around potential minimum

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3.2 The resistively and capacitively shunted junction (RCSJ) model

The pendulum analog

- Plane mechanical pendulum in uniform gravitational field
- Mass m , length ℓ , deflection angle θ
- Torque D parallel to rotation axis
- Restoring torque: $mg\ell \sin \theta$

Equation of motion → $D = \Theta \ddot{\theta} + \Gamma \dot{\theta} + mg\ell \sin \theta$

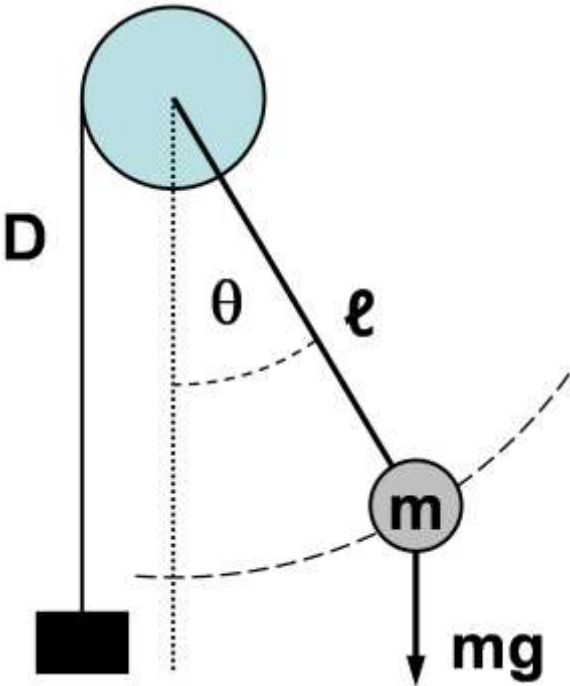
$\Theta = m\ell^2$ Moment of inertia
 Γ Damping constant

Analogies	I	↔	D
	I_c	↔	$mg\ell$
	$\frac{\Phi_0}{2\pi R}$	↔	Γ
	$\frac{C\Phi_0}{2\pi}$	↔	Θ
	φ	↔	θ

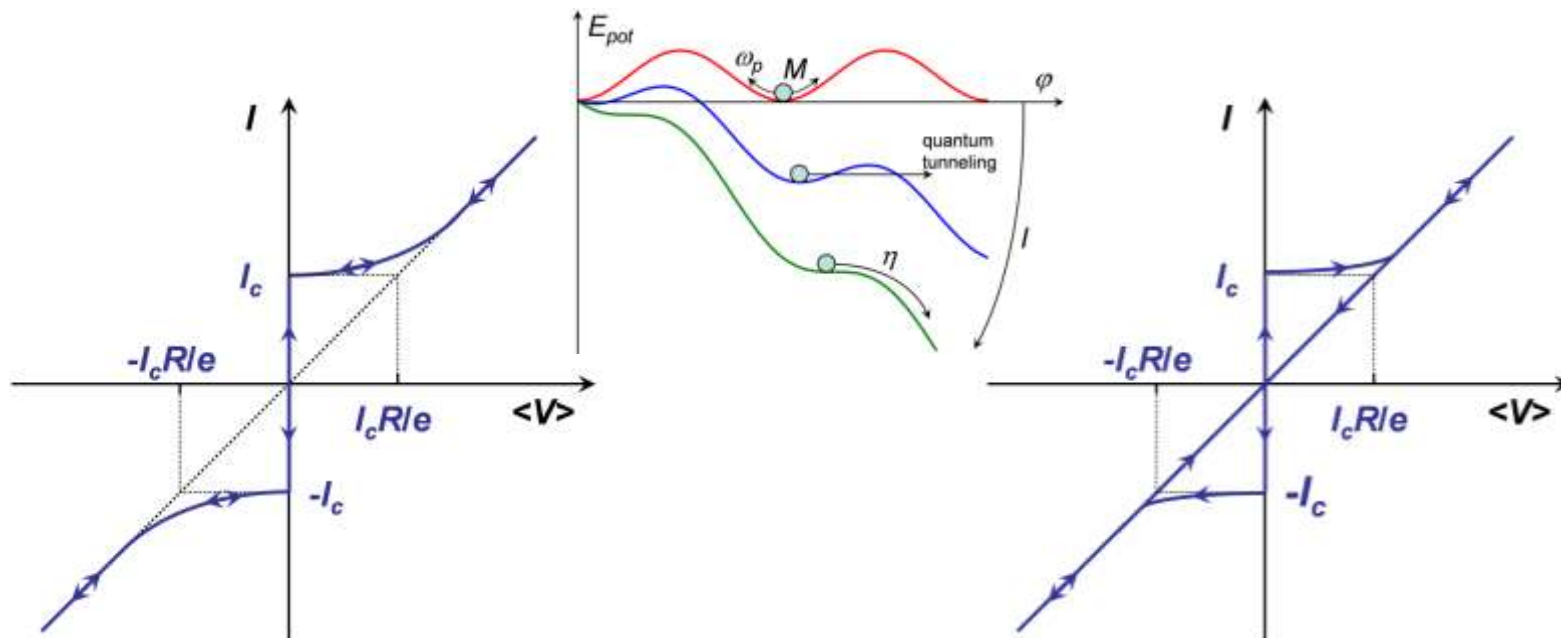
For $D = 0$ → Oscillations around equilibrium with

$$\omega = \sqrt{\frac{g}{\ell}} \leftrightarrow \text{Plasma frequency } \omega_p = \sqrt{\frac{2\pi I_c}{\Phi_0 C}}$$

Finite torque ($D > 0$) → Finite θ_0 → Finite, but constant φ_0 → Zero-voltage state
 Large torque (deflection $> 90^\circ$) → Rotation of the pendulum → Finite-voltage state
 Voltage V ↔ Angular velocity of the pendulum



3.2.1 Under- and overdamped Josephson junctions



Overdamped junction

$$\beta_C = \frac{2eI_c R^2 C}{\hbar} \ll 1$$

Capacitance & resistance small

→ M small, η large

→ Non-hysteretic IVC

(Phase particle will retrap immediately at I_c because of large damping)

Underdamped junction

$$\beta_C = \frac{2eI_c R^2 C}{\hbar} \gg 1$$

→ Capacitance & resistance large

→ M large, η small

→ Hysteretic IVC

(Once the phase is moving, the potential has to be tilted back almost into the horizontal position to stop its motion)

3.3 Response to driving sources

Motivation

„Applied Superconductivity“ → One central question is

→ „How to extract information about the junction experimentally?“

Typical strategy

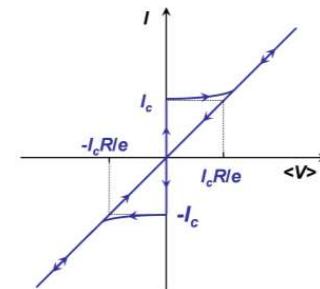
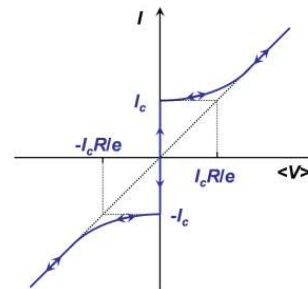
→ Drive junction with a probe signal and measure response

Examples for probe signals

- Currents (magnetic fields)
- Voltages (electric fields)
- DC or AC
- Josephson junctions → AC means microwaves!

Prototypical experiment

- Measure junction IVC
- Typically done with current bias



3.3.1 Response to a dc current source

$T = \text{Oscillation period}$

Time averaged voltage:

$$\langle V \rangle = \frac{1}{T} \int_0^T V(t) dt = \frac{1}{T} \int_0^T \frac{\hbar}{2e} \frac{d\varphi}{dt} dt = \frac{1}{T} \frac{\hbar}{2e} \overbrace{[\varphi(T) - \varphi(0)]}^{2\pi} = \frac{\Phi_0}{T}$$

Total current must be constant (neglecting the fluctuation source):

$$I = I_s(t) + I_N(t) + I_D(t) = I_c \sin \varphi(t) + \frac{V(t)}{R} + C \frac{dV(t)}{dt} = \text{const}$$

$$\text{where: } \varphi(t) = \int_0^t \frac{2e}{\hbar} V(t) dt$$

$I > I_c \rightarrow$ Part of the current must flow as I_N or I_D

\rightarrow Finite junction voltage $|V| > 0$

\rightarrow Time varying I_s

$\rightarrow I_N + I_D$ varies in time

\rightarrow Time varying voltage, complicated non-sinusoidal oscillations of I_s ,

Oscillating voltage has to be calculated self-consistently

\rightarrow Oscillation frequency $f = \langle V \rangle / \Phi_0$

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3.3.1 Response to a dc current source

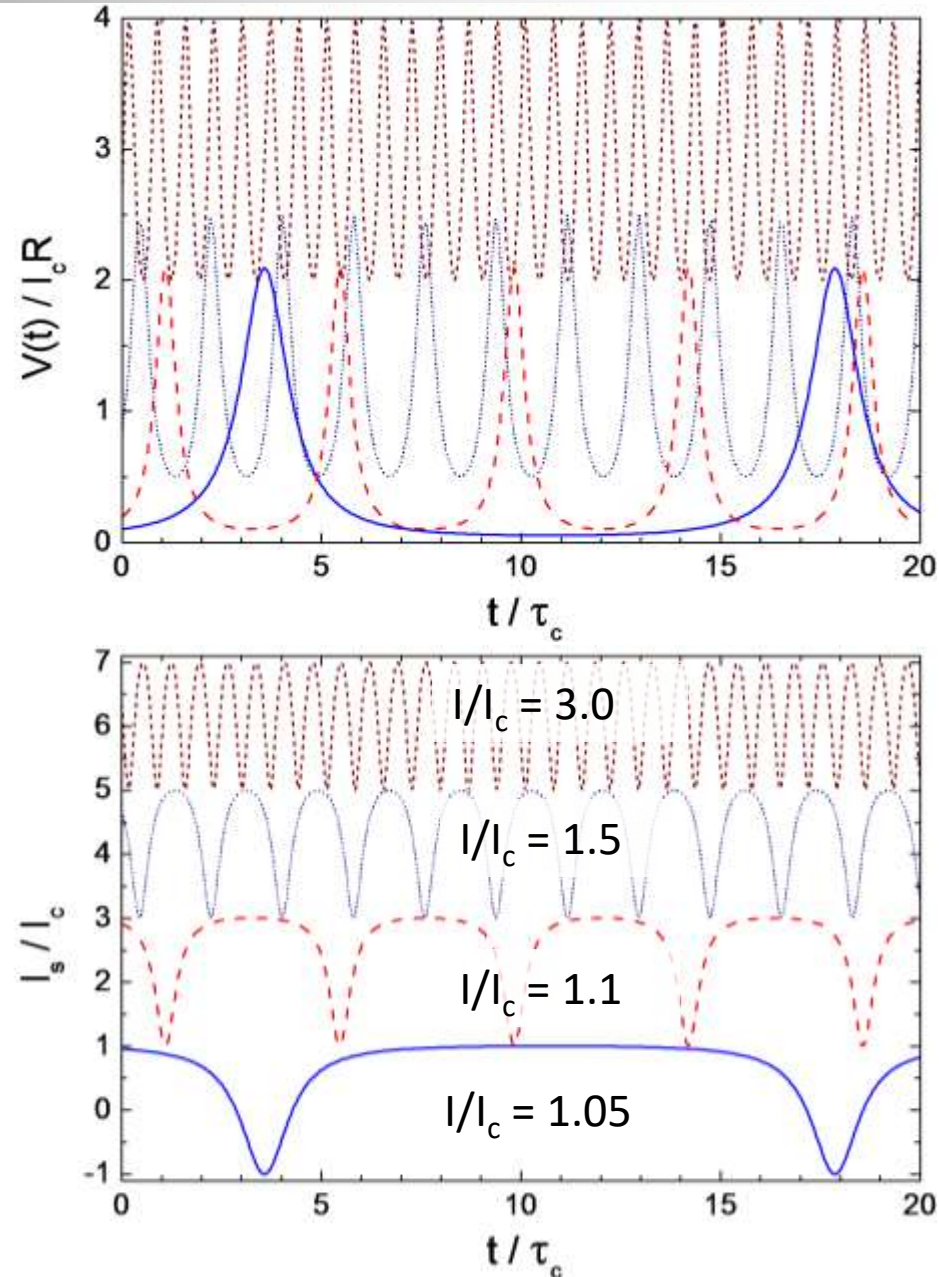
For $I \gtrsim I_c$

- Highly non-sinusoidal oscillations
- Long oscillation period
- $\langle V \rangle \propto \frac{1}{T}$ is small

For $I \gg I_c$

- Almost all current flows as normal current
- Junction voltage is nearly constant
- Almost sinusoidal Josephson current oscillations
- Time averaged Josephson current almost zero
- Linear/Ohmic IVC

→ Analogy to pendulum



3.3.1 Response to a dc current source

Strong damping

$\beta_c \ll 1$ & neglecting noise current

$$\cancel{\beta_c \frac{d^2\varphi}{d\tau^2}} + \frac{d\varphi}{d\tau} + \sin\varphi - i = 0$$

$i < 1 \rightarrow$ Only supercurrent, $\varphi = \sin^{-1} i$ is a solution, zero junction voltage

$i > 1 \rightarrow$ Finite voltage, temporal evolution of the phase

$$d\tau = \frac{d\varphi}{i - \sin\varphi}$$

Integration using

$$\int \frac{dx}{a - \sin x} = \frac{2}{\sqrt{a^2 - 1}} \tan^{-1} \left(\frac{-1 + a \tan(x/2)}{\sqrt{a^2 - 1}} \right)$$

gives

$$\tau - \tau_0 = \frac{2}{\sqrt{i^2 - 1}} \tan^{-1} \left(\frac{-1 + i \tan(\varphi/2)}{\sqrt{i^2 - 1}} \right)$$

Setting $\tau_0 = 0$ and using $\tau = \frac{t}{\tau_c}$

$$\Rightarrow \varphi(t) = 2 \tan^{-1} \left\{ \sqrt{1 - \frac{1}{i^2}} \tan \left(\frac{t\sqrt{i^2 - 1}}{2\tau_c} \right) + \frac{1}{i} \right\}$$

Periodic function with period

$$T = \frac{2\pi\tau_c}{\sqrt{i^2 - 1}}$$

$\tan^{-1}(a \tan x + b)$
is π -periodic

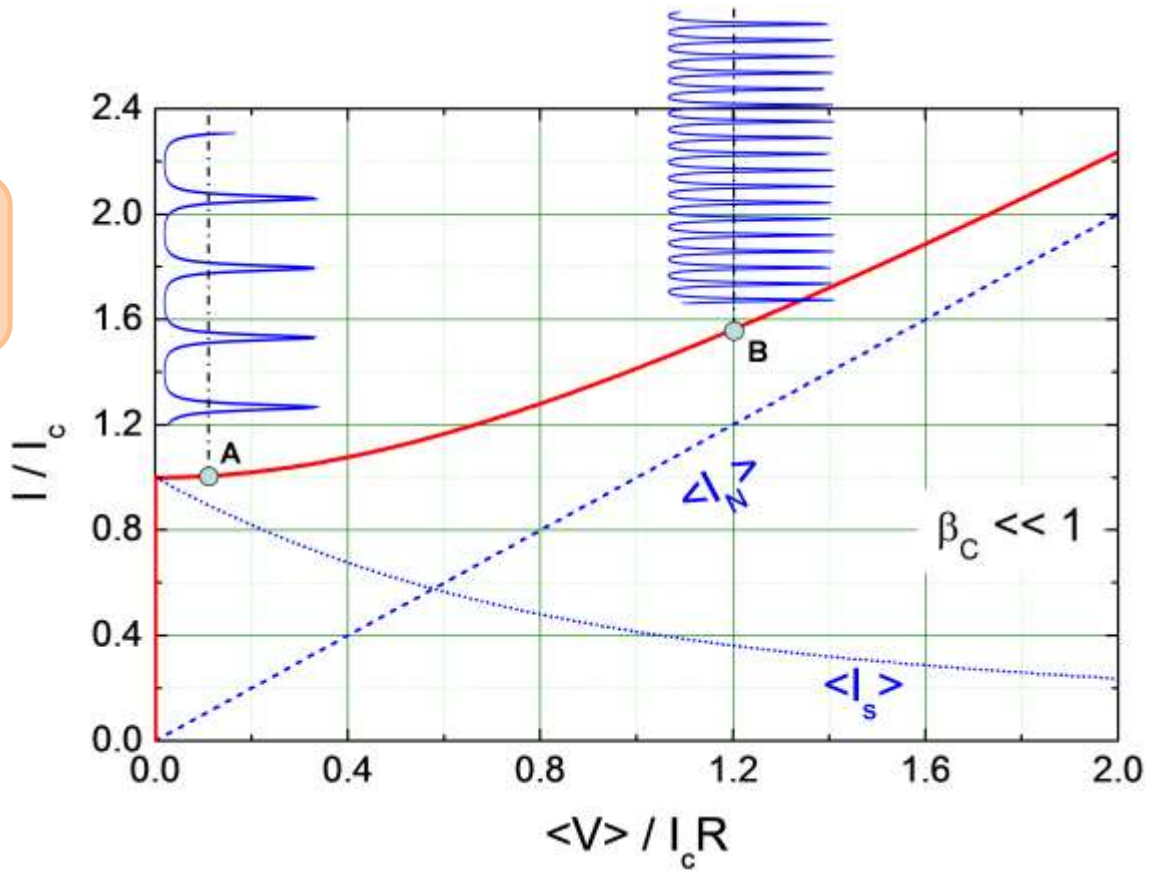
3.3.1 Response to a dc current source

with $\langle V(t) \rangle = \frac{1}{T} \int_0^T V(t) dt = \frac{\Phi_0}{T}$

and $\tau_c = \frac{\Phi_0}{2\pi I_c R}$ $T = \frac{2\pi\tau_c}{\sqrt{i^2 - 1}}$

We get for $i > 1$

$$\langle V(t) \rangle = I_c R \sqrt{\left(\frac{I}{I_c}\right)^2 - 1}$$



3.3.1 Response to a dc current source

Weak damping

$\beta_C \gg 1$ & neglecting noise current

$\omega_{RC} = \frac{1}{R_N C}$ is very small

→ Large C is effectively shunting oscillating part of junction voltage → $V(t) \simeq \bar{V}$

→ Time evolution of the phase

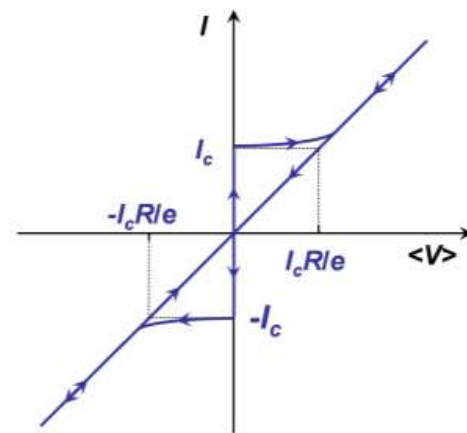
$$\varphi(t) = \frac{2e}{\hbar} \bar{V} t + \text{const}$$

→ Almost sinusoidal oscillation of Josephson current

$$\overline{I_s(t)} = \overline{I_c \sin\left(\frac{2e}{\hbar} \bar{V} t + \text{const}\right)} \simeq 0$$

→ Down to $\bar{V} \approx \frac{\hbar \omega_{RC}}{e} \ll (V_C = I_c R_N) \Rightarrow \bar{I} = I_N(\bar{V}) = \frac{\bar{V}}{R}$

→ Corresponding current $\ll I_c \rightarrow$ **Hysteretic IVC**



Ohmic result valid for $R_N = \text{const.}$

→ Real junction → IVC determined by voltage dependence of $R_N = R_N(V)$

3.3.1 Response to a dc current source

Intermediate damping

$$\beta_C \approx 1$$

→ Numerically solve IVC

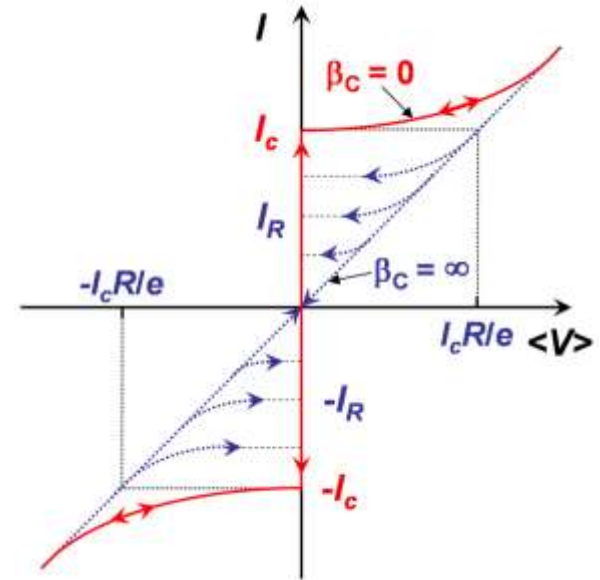
→ General trend

Increasing $\beta_C \leftrightarrow$ Increasing hysteresis

Hysteresis characterized by retrapping current I_R

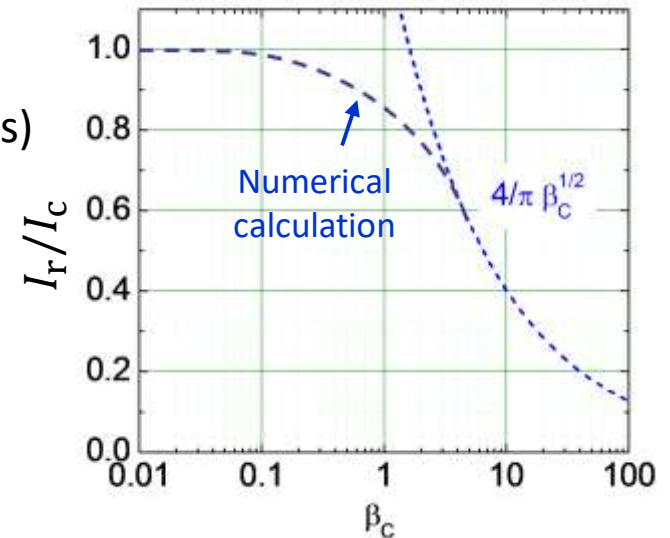
→ $I_R \propto$ washboard potential tilt where

Energy dissipated in advancing to next minimum = Work done by drive current



Analytical calculation possible for $\beta_C \gg 1$ (exercise class)

$$\frac{I_R}{I_c} = \frac{4}{\pi} \frac{1}{\sqrt{\beta_C}}$$



3.3.1 Response to a dc **voltage** source

Phase evolves linearly in time: $\varphi(t) = \frac{2e}{\hbar} V_{dc} t + \text{const}$

→ Josephson current I_S oscillates sinusoidally

→ Time average of I_S is zero

→ $I_D = 0$ since $\frac{dV_{dc}}{dt} = 0$

→ Total current carried by normal current $\rightarrow I = \frac{V_{dc}}{R_N}$

RCSJ model

→ Ohmic IVC

General case $R = R_N(V)$

→ Nonlinear IVC

3.3.2 Response to **ac** driving sources

Response to an ac voltage source

Strong damping $\beta_C \ll 1$

$$V(t) = V_{\text{dc}} + V_1 \cos \omega_1 t$$

Integrating the voltage-phase relation:

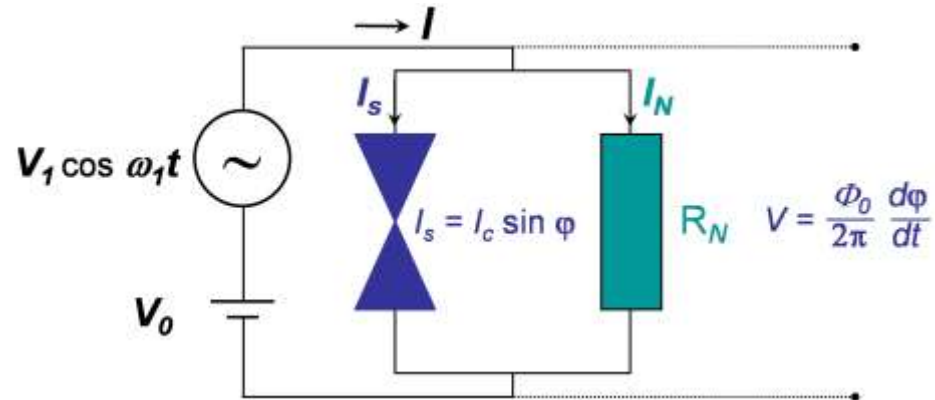
$$\varphi(t) = \varphi_0 + \frac{2\pi}{\Phi_0} V_{\text{dc}} t + \frac{2\pi}{\Phi_0} \frac{V_1}{\omega_1} \sin \omega_1 t$$

Current-phase relation:
$$I_s(t) = I_c \sin \left\{ \varphi_0 + \frac{2\pi}{\Phi_0} V_{\text{dc}} t + \frac{2\pi}{\Phi_0} \frac{V_1}{\omega_1} \sin \omega_1 t \right\}$$

Superposition of **linearly increasing** and **sinusoidally varying** phase

→ Supercurrent $I_s(t)$ and ac voltage V_1 have different frequencies

→ Origin → Nonlinear current-phase relation



3.3.2 Response to ac driving sources

Some maths for the analysis of the time-dependent Josephson current

Fourier-Bessel series identity:
$$e^{ib \sin x} = \sum_{n=-\infty}^{+\infty} \mathcal{J}_n(b) e^{inx}$$

$\mathcal{J}_n(b) = n^{\text{th}}$ order Bessel function of the first kind

and:
$$\sin(a + b \sin x) = \Im \left\{ e^{i(a + b \sin x)} \right\}$$

$\mathcal{J}_{-n}(b) = (-1)^n \mathcal{J}_n(b)$

$$\Rightarrow e^{i(a + b \sin x)} = \sum_{n=-\infty}^{+\infty} \mathcal{J}_n(b) e^{i(a + nx)} = \sum_{n=-\infty}^{+\infty} (-1)^n \mathcal{J}_n(b) e^{i(a - nx)}$$

$$\Rightarrow \sin(a + b \sin x) = \sum_{n=-\infty}^{+\infty} (-1)^n \mathcal{J}_n(b) \sin(a - nx)$$

Imaginary part

Ac driven junction $\rightarrow x = \omega_1 t$, $b = \frac{2\pi}{\Phi_0 \omega_1}$ and $a = \varphi_0 + \omega_{dc} t = \varphi_0 + \frac{2\pi}{\Phi_0} V_{dc} t$

$$I_s(t) = I_c \sum_{n=-\infty}^{+\infty} (-1)^n \mathcal{J}_n \left(\frac{2\pi V_1}{\Phi_0 \omega_1} \right) \sin [(\omega_{dc} - n\omega_1)t + \varphi_0]$$

\rightarrow Frequency ω_{dc} **couple to multiples** of the driving frequency

3.3.2 Response to ac driving sources

Shapiro steps

$$I_s(t) = I_c \sum_{n=-\infty}^{+\infty} (-1)^n \mathcal{J}_n \left(\frac{2\pi V_1}{\Phi_0 \omega_1} \right) \sin [(\omega_{dc} - n\omega_1)t + \varphi_0]$$

→ Ac voltage results in dc supercurrent if $[(\omega_{dc} - n\omega_1)t + \varphi_0]$ is time independent

$$\omega_{dc} = n\omega_1 \quad \text{or} \quad V_{dc} = V_n = n \frac{\Phi_0}{2\pi} \omega_1$$

→ Amplitude of average dc current for a specific step number n

$$|\langle I_s \rangle_n| = I_c \left| \mathcal{J}_n \left(\frac{2\pi V_1}{\Phi_0 \omega_1} \right) \right|$$

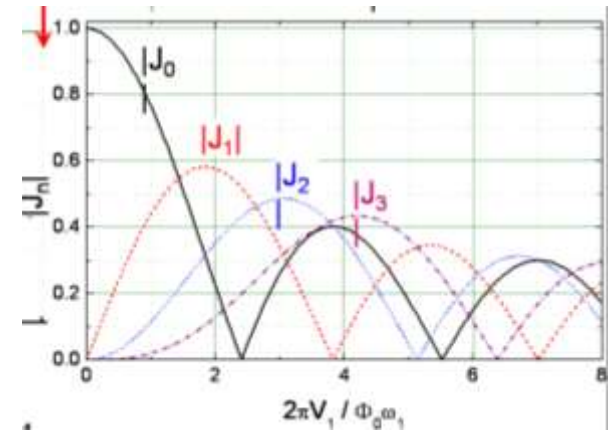
$$V_{dc} \neq V_n$$

→ $[(\omega_{dc} - n\omega_1)t + \varphi_0]$ is time dependent

→ Sum of sinusoidally varying terms

→ Time average is zero

$$\text{→ Vanishing dc component} \rightarrow \langle I \rangle = \frac{V_{dc}}{R_N} + \left\langle \frac{V_1}{R_N} \cos \omega_1 t \right\rangle = \frac{V_{dc}}{R_N}$$

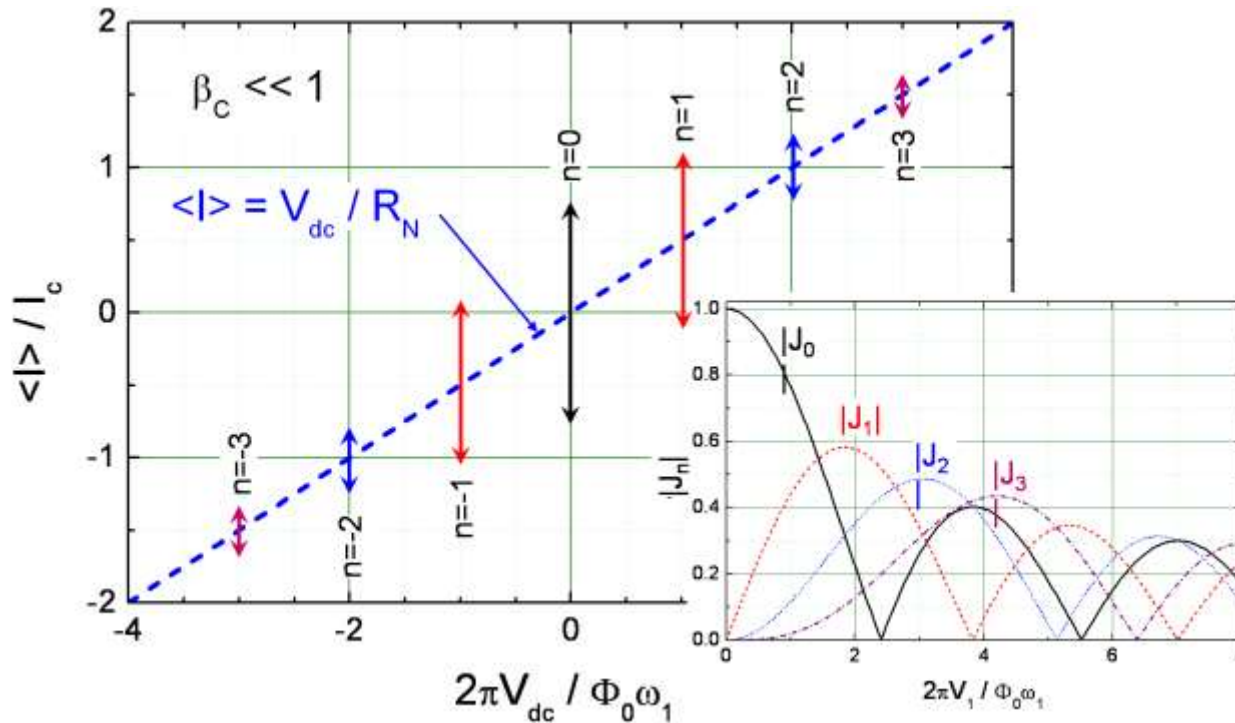


3.3.2 Response to ac driving sources

- Ohmic dependence with **sharp current spikes** at $V_{dc} = V_n$
- Current **spike amplitude depends on ac voltage amplitude**
- n^{th} step → Phase locking of the junction to the n^{th} harmonic

$$V_n = n \frac{\Phi_0}{2\pi} \omega_1$$

$$|\langle I_s \rangle_n| = I_c \left| \mathcal{J}_n \left(\frac{2\pi V_1}{\Phi_0 \omega_1} \right) \right|$$



Example: $\omega_1/2\pi = 10$ GHz

Constant dc current at $V_{dc} = 0$ and $V_n = n\omega_1 \frac{\Phi_0}{2\pi} \approx n \times 20 \mu\text{V}$

3.3.2 Response to ac driving sources

Response to an ac current source

Strong damping $\beta_C \ll 1$ (experimentally relevant)

→ Kirchhoff's law (neglecting I_D) → $I_C \sin \varphi + \frac{1}{R_N} \frac{\Phi_0}{2\pi} \frac{d\varphi}{dt} = I_{dc} + I_1 \sin \omega_1 t$

Difficult to solve → Qualitative discussion with washboard potential

→ Increase I_{dc} at constant I_1

→ Zero-voltage state for $I_{dc} + I_1 \leq I_C$, finite voltage state for $I_{dc} + I_1 > I_C$

→ **Complicated dynamics!**

→ $V_n = n\omega_1 \frac{\Phi_0}{2\pi}$ → Motion of phase particle **synchronized** by ac driving

Simplifying assumption

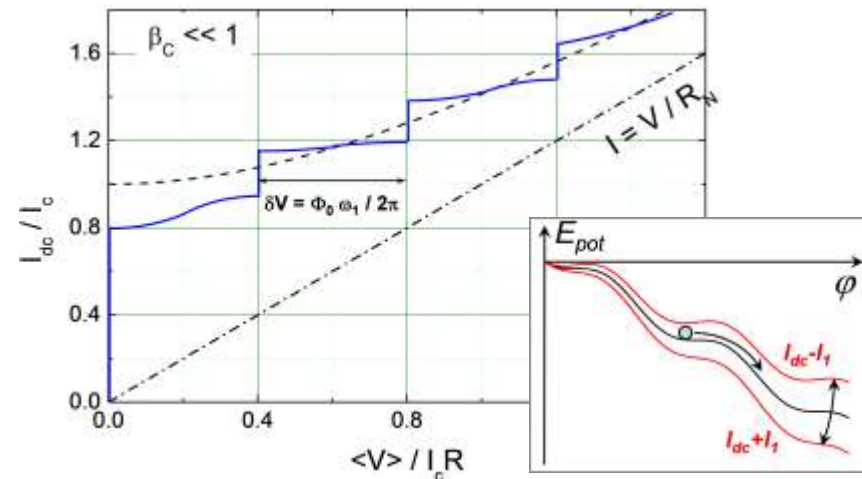
→ During each ac cycle the phase particle moves down n minima

→ Resulting phase change $\dot{\varphi} = n \frac{2\pi}{T} = n\omega_1$

→ **Average dc voltage** $\langle V \rangle = n \frac{\Phi_0}{2\pi} \omega_1 \equiv V_n$

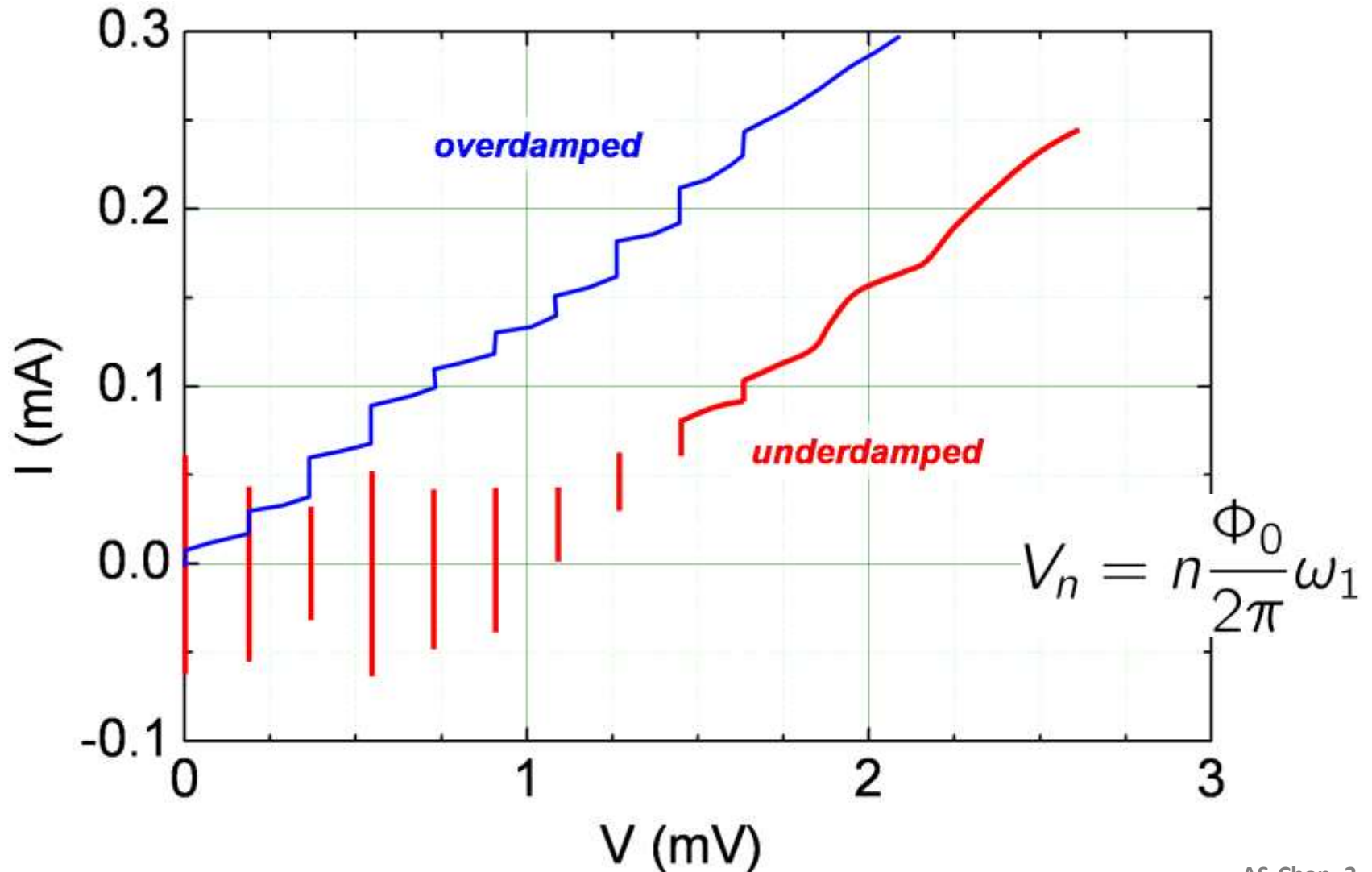
Exact analysis

→ **Synchronization** of phase dynamics with external ac source for a certain bias current interval → **Steps**



3.3.2 Response to ac driving sources

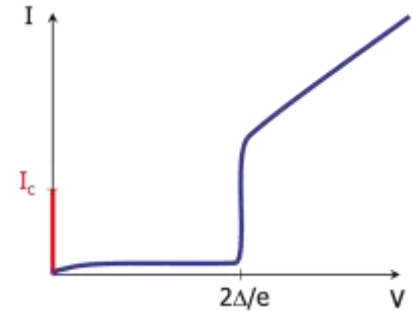
Experimental IVCs obtained for an overdamped and overdamped Niobium Josephson junction under microwave irradiation



3.3.4 Photon-assisted tunneling

Superconducting tunnel junction \rightarrow **Highly nonlinear $R(V)$**

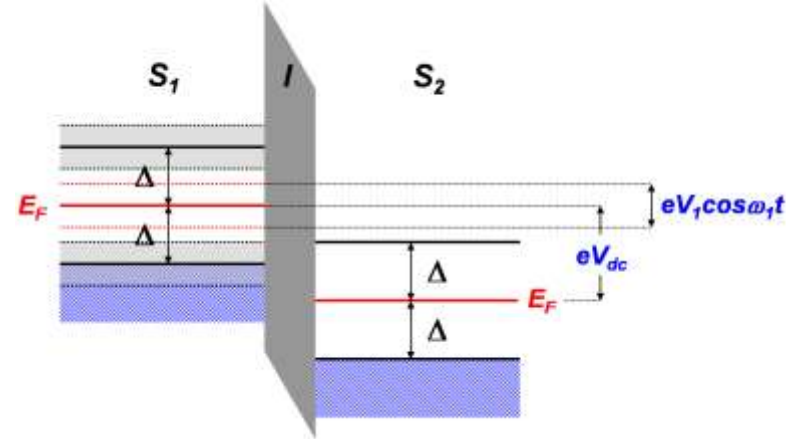
- \rightarrow Sharp step at $V_g = \frac{2\Delta}{e}$
- \rightarrow Use quasiparticle (QP) tunneling current $I_{qp}(V)$
- \rightarrow Include **effect of ac source** on QP tunneling



Model of Tien and Gordon:

- \rightarrow Ac driving shifts levels in electrode up and down
- QP energy: $E_{qp} + eV_1 \cos \omega_1 t$
- \rightarrow QM phase factor

$$\exp\left(-\frac{i}{\hbar} \int (E_{qp} + eV_1 \cos \omega_1 t) dt\right) = \exp\left(-\frac{i}{\hbar} E_{qp} t\right) \cdot \exp\left(-i \frac{eV_1}{\hbar \omega_1} \sin \omega_1 t\right)$$



Bessel function identity for V_1 -term \rightarrow Sum of terms $\mathcal{J}_n(eV_1/\hbar\omega_1) e^{-in\omega_1 t}$

\rightarrow **Splitting** of qp-levels into **many levels** $E_{qp} \pm n\hbar\omega_1 \rightarrow$ Modified density of states!

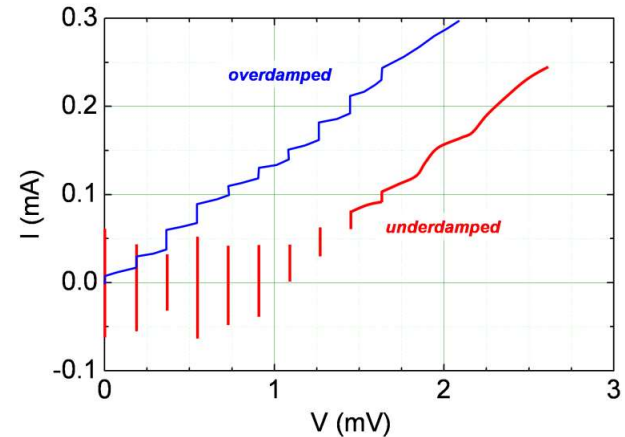
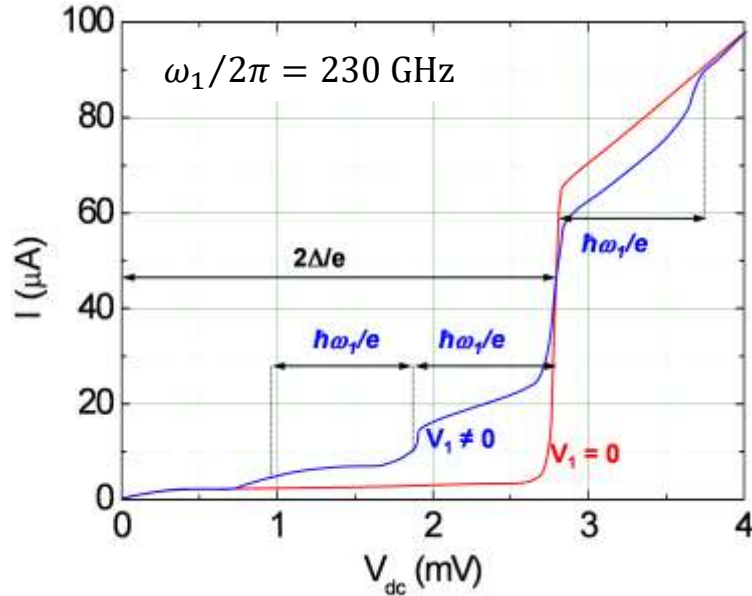
\rightarrow Tunneling current $I_{qp}(V) = \sum_{n=-\infty}^{+\infty} \mathcal{J}_n^2\left(\frac{eV_1}{\hbar\omega_1}\right) I_{qp}^0(V + n\hbar\omega_1/e)$

\rightarrow Sharp increase of the $I_{qp}(V)$ at $V = V_g$ is broken up into **many steps of smaller current amplitude** at $V_n = V_g \pm \frac{n\hbar\omega_1}{e}$

3.3.4 Photon-assisted tunneling

Example

- QP IVC of a Nb SIS Josephson junction without & with microwave irradiation
- Frequency $\omega_1/2\pi = 230$ GHz corresponding to $\hbar\omega_1/e \simeq 950 \mu\text{V}$



QP steps

- Appear at $V_n = n \frac{\hbar}{e} \omega_1$
- Amplitude $J_n \left(\frac{eV_1}{\hbar\omega_1} \right)$
- Broadened steps (depending on $I_{qp}(V)$)

Shapiro steps

- Appear at $V_n = n \frac{\hbar}{2e} \omega_1$
- Amplitude $J_n \left(\frac{2eV_1}{\hbar\omega_1} \right)$
- Sharp steps

3.4 Effect of thermal fluctuations

Thermal fluctuations with correlation function:

$$\langle I_F(t) I_F(t + \tau) \rangle = \frac{2k_B T}{R_N} \delta(\tau)$$

Small fluctuations → Phase fluctuations around equilibrium

$$S(f) = 4k_B T / R_N$$

Larger fluctuations

→ Increase probability for escape out of potential well

- Escape at rates $\Gamma_{n\pm 1}$
 - Escape to next minimum
 - Phase change of 2π

$$\rightarrow I > 0 \rightarrow \Gamma_{n+1} > \Gamma_{n-1} \rightarrow \left\langle \frac{d\varphi}{dt} \right\rangle > 0$$

Langevin equation for RCSJ model

$$I = I_c \sin \varphi + \frac{1}{R_N} \frac{\Phi_0}{2\pi} \frac{d\varphi}{dt} + C \frac{\Phi_0}{2\pi} \frac{d^2\varphi}{dt^2} + I_F$$

→ Equivalent to Fokker-Planck equation:

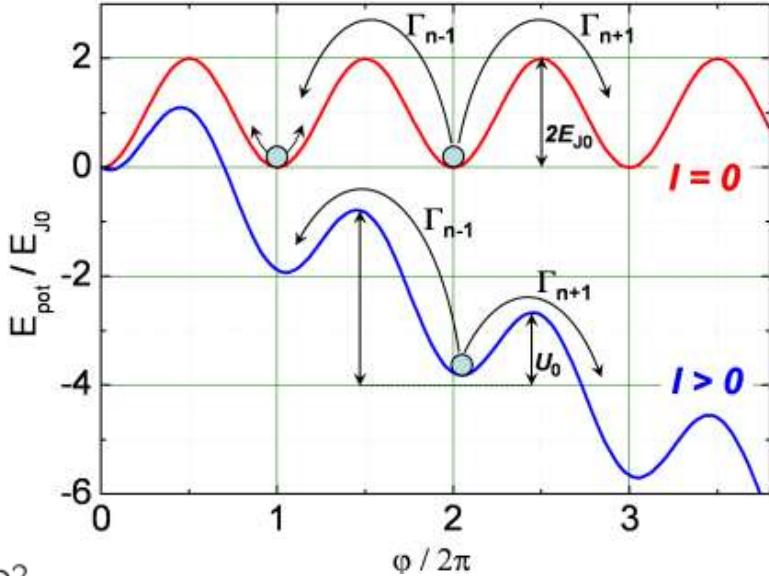
$$\frac{1}{\omega_c} \frac{\partial \sigma}{\partial t} + \frac{\partial}{\partial \varphi} (\sigma v) + \frac{1}{\beta_C} \frac{\partial}{\partial v} (\sigma [f(\varphi) - v]) = \frac{\gamma}{\beta_C^2} \frac{\partial^2 \sigma}{\partial v^2}$$

Normalized force

$$f(\varphi) = -\frac{1}{E_{J0}} \frac{\partial U(\varphi)}{\partial \varphi} = \frac{I}{I_c} - \sin \varphi$$

Normalized momentum

$$v = \frac{d\varphi/dt}{\omega_c} = \frac{V}{I_c R_N}$$



3.4 Effect of thermal fluctuations

$\sigma(v, \varphi, t) \rightarrow$ **Probability density** of finding system at (v, φ) at time t

$$\langle X \rangle(t) = \iint_{-\infty}^{+\infty} \sigma(\varphi, v, t) X(\varphi, v, t) d\varphi dv$$

statistical average of variable X

Small fluctuations

\rightarrow Static solution ($\frac{d\sigma}{dt} = 0$) $\sigma(v, t) = \mathcal{F}^{-1} \exp\left(-\frac{G(\varphi, \sigma)}{k_B T}\right)$

with: $\mathcal{F} = \iint_{-\infty}^{+\infty} \exp\left(-\frac{G(\varphi, \sigma)}{k_B T}\right) d\varphi dv$

\rightarrow **Boltzmann distribution** ($G = E - Fx$ is total energy, E is free energy)

\rightarrow Constant probability to find system in n^{th} metastable state

$$p = \int_{-\infty}^{+\infty} dv \int_{\varphi \approx \varphi_n} \sigma(\varphi, v) d\varphi$$

3.4 Effect of thermal fluctuations

Large fluctuations

p can change in time $\rightarrow \frac{dp}{dt} = (\Gamma_{n+1} - \Gamma_{n-1})p$

Amount of phase slippage

for $\Gamma_{n+1} \gg \Gamma_{n-1}$ and $\frac{\omega_A}{\Gamma_{n+1}} \gg 1 \rightarrow \Gamma_{n+1} = \frac{\omega_A}{2\pi} \exp\left(-\frac{U_0}{k_B T}\right)$

Kramers approximation
 $\omega_A =$ Attempt frequency

Attempt frequency ω_A

$$\omega_A = \omega_0 = \omega_p(1 - i^2)^{1/4} \quad \text{for } \omega_c \tau \gg 1, \quad (\text{underdamped junction})$$

$$\omega_A = \tau^{-1} = \omega_c(1 - i^2)^{1/2} \quad \text{for } \omega_c \tau \ll 1 \quad (\text{overdamped junction})$$

Weak damping ($\beta_C = \omega_c \tau_{RC} \gg 1$)

$\rightarrow I = 0 \rightarrow \omega_A = \omega_p$ (Oscillation frequency in the potential well)

$\rightarrow I \ll I_c \rightarrow \omega_A \gg \omega_p$

Strong damping ($\beta_C = \omega_c \tau_{RC} \ll 1$)

$\rightarrow \omega_p \rightarrow \omega_c$ (Frequency of an overdamped oscillator)

3.4.1 Underdamped junctions:

Critical current reduction by premature switching

For $E_{J0} \gg k_B T \rightarrow$ Small escape probability $\propto \exp\left(-\frac{U_0(I)}{k_B T}\right)$ at each attempt

Barrier height: $U_0(I) \simeq 2E_{J0} \left(1 - \frac{I}{I_c}\right)^{3/2}$

$\rightarrow 2E_{J0}$ for $I = 0$
 $\rightarrow 0$ for $I \rightarrow I_c$

Escape probability $\rightarrow \omega_A/2\pi$ for $I \rightarrow I_c$

After escape \rightarrow Junction switches to IR_N

Experiment

\rightarrow Measure distribution of escape current I_M
 \rightarrow Width δI and mean reduction $\langle \Delta I_c \rangle = I_c - \langle I_M \rangle$

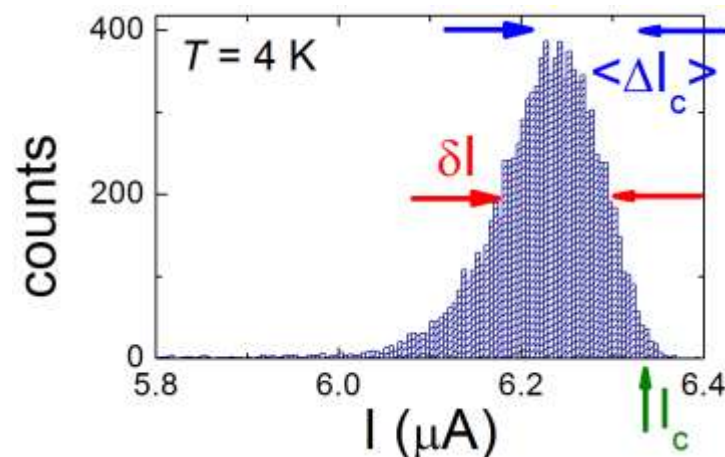
\rightarrow Use approximation for $U_0(I)$ and escape rate

$$\omega_A/2\pi \exp\left(-\frac{U_0(I)}{k_B T}\right)$$

$$\langle \Delta I_c \rangle = I_c - \langle I_M \rangle \simeq I_c \left[\frac{k_B T}{2E_{J0}} \ln\left(\frac{\omega_p \Delta t}{2\pi}\right) \right]^{2/3}$$

\rightarrow Considerable reduction of I_c when $k_B T > 0.05 E_{J0}$

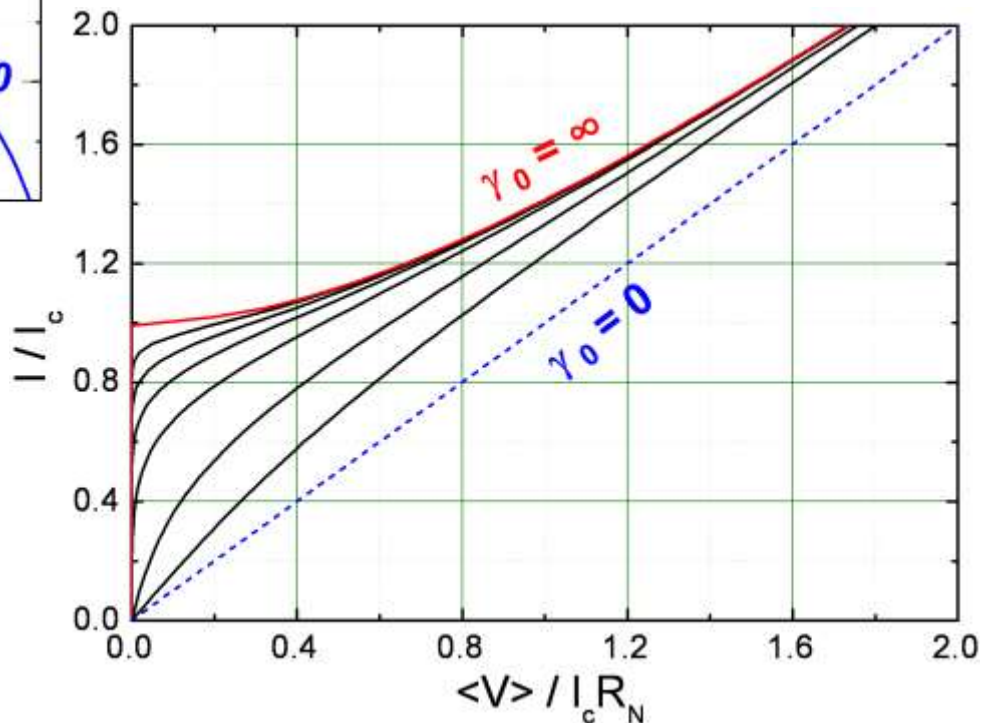
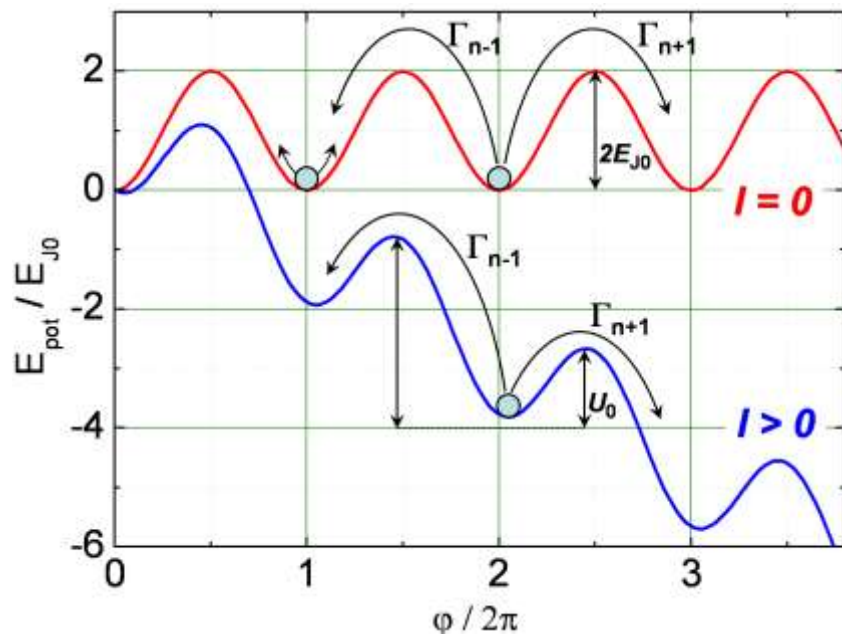
\rightarrow Provides experimental information on real or effective temperature!



3.4.2 Additional topic:

Overdamped junctions - The Ambegaokar-Halperin theory

Calculate voltage $\langle V \rangle$ induced by thermally activated phase slips as a function of current



Important parameter:

$$\gamma_0(T) = \frac{2E_{J0}(T)}{k_B T} = \frac{\Phi_0 I_c(T)}{\pi k_B T}$$

3.4.2 Additional topic:

Overdamped junctions - The Ambegaokar-Halperin theory

Ambegaokar-Halperin theory

Finite amount of **phase slippage**

→ Nonvanishing voltage for $I \rightarrow 0$

→ Phase slip resistance for strong damping ($\beta_C \ll 1$), for $U_0 = 2E_{J0}$:

$$R_p = \lim_{I \rightarrow 0} \frac{\langle V \rangle}{I} = R_N \left\{ \mathcal{I}_0 \left[\frac{\gamma_0(T)}{2} \right] \right\}^{-2} \quad \gamma_0(T) = \frac{2E_{J0}(T)}{k_B T} = \frac{\Phi_0 I_c(T)}{\pi k_B T}$$

Modified Bessel function

$$\frac{E_{J0}}{k_B T} \gg 1 \rightarrow \text{Approximate Bessel function} \rightarrow \mathcal{I}_0(x) = e^x / 2\pi\sqrt{x}$$

$$\frac{R_p(T)}{R_N} \propto E_{J0} \exp\left(-\frac{2E_{J0}}{k_B T}\right)$$

attempt frequency

$$\text{or } \langle \dot{\varphi} \rangle \propto \frac{2eI_c R_N}{\hbar} \exp\left(-\frac{2E_{J0}}{k_B T}\right) = \omega_c \exp\left(-\frac{2E_{J0}}{k_B T}\right)$$

Attempt frequency is characteristic frequency ω_c

Plasma frequency has to be replaced by frequency of overdamped oscillator:

$$\omega_A = \omega_p \sqrt{\beta_C} = \omega_p \sqrt{\omega_c R_N C} = \omega_c$$

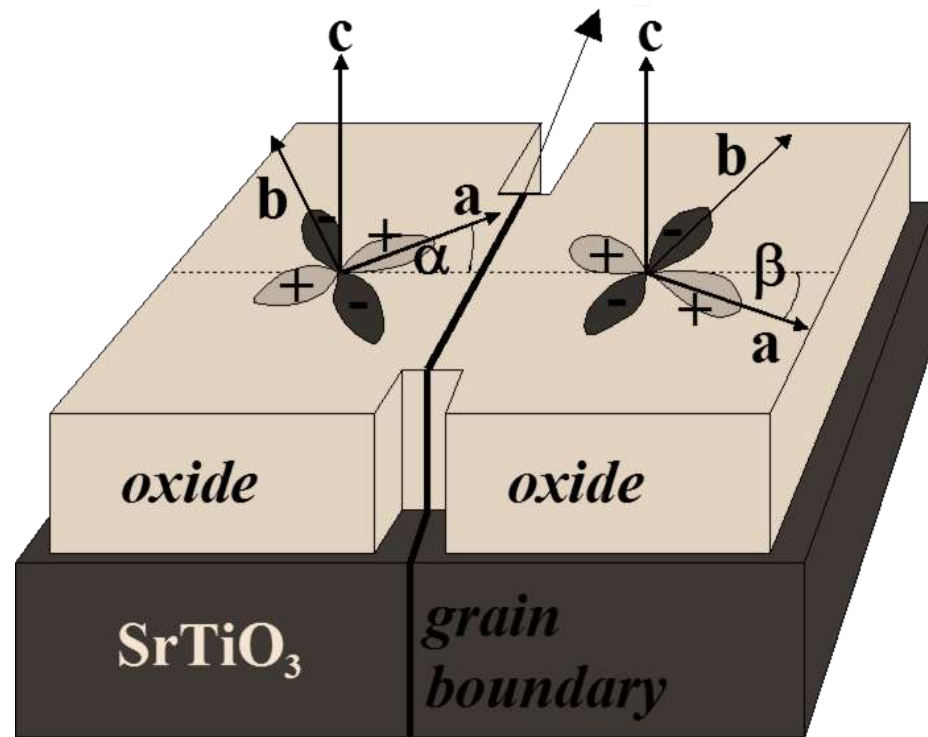
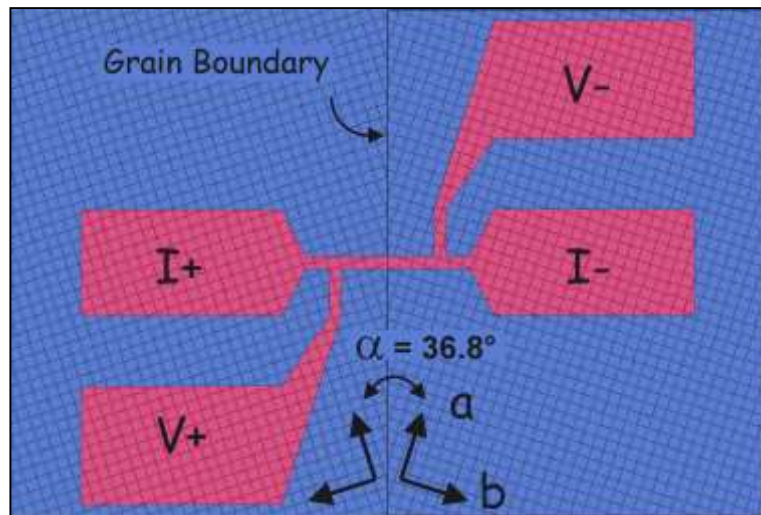
Washboard potential → Phase diffuses over barrier → Activated nonlinear resistance

3.4.2 Additional topic:

Overdamped junctions - The Ambegaokar-Halperin theory

Example: $\text{YBa}_2\text{Cu}_3\text{O}_7$ grain boundary Josephson junctions

→ Strong effect of thermal fluctuations due to high operation temperature



epitaxial $\text{YBa}_2\text{Cu}_3\text{O}_7$ film on
 SrTiO_3 bicrystalline substrate

R. Gross et al.,

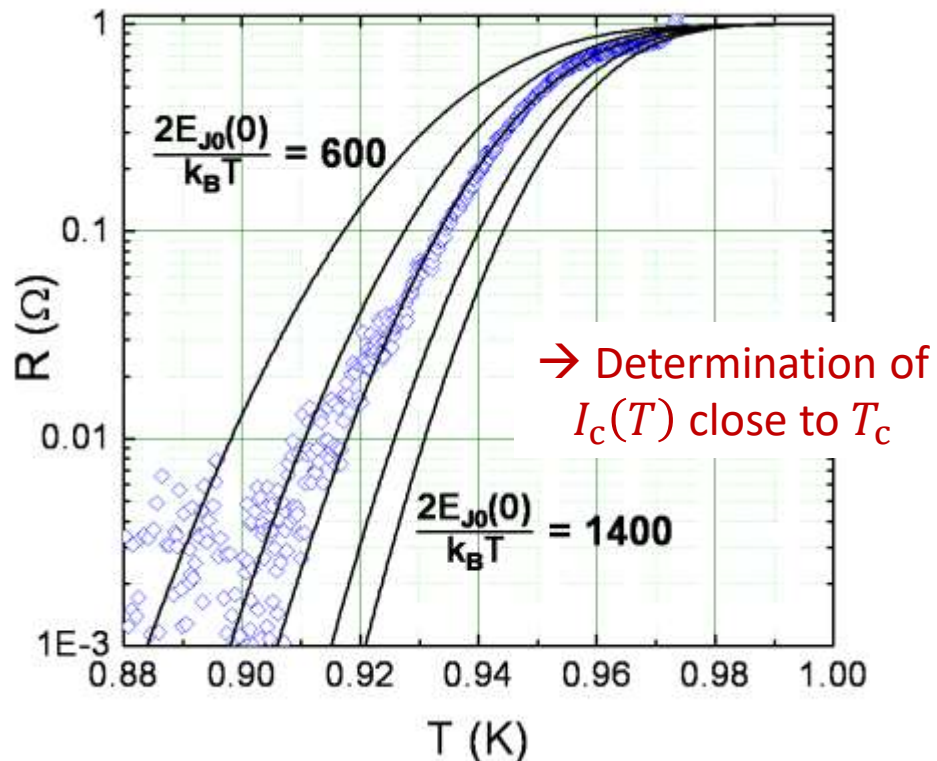
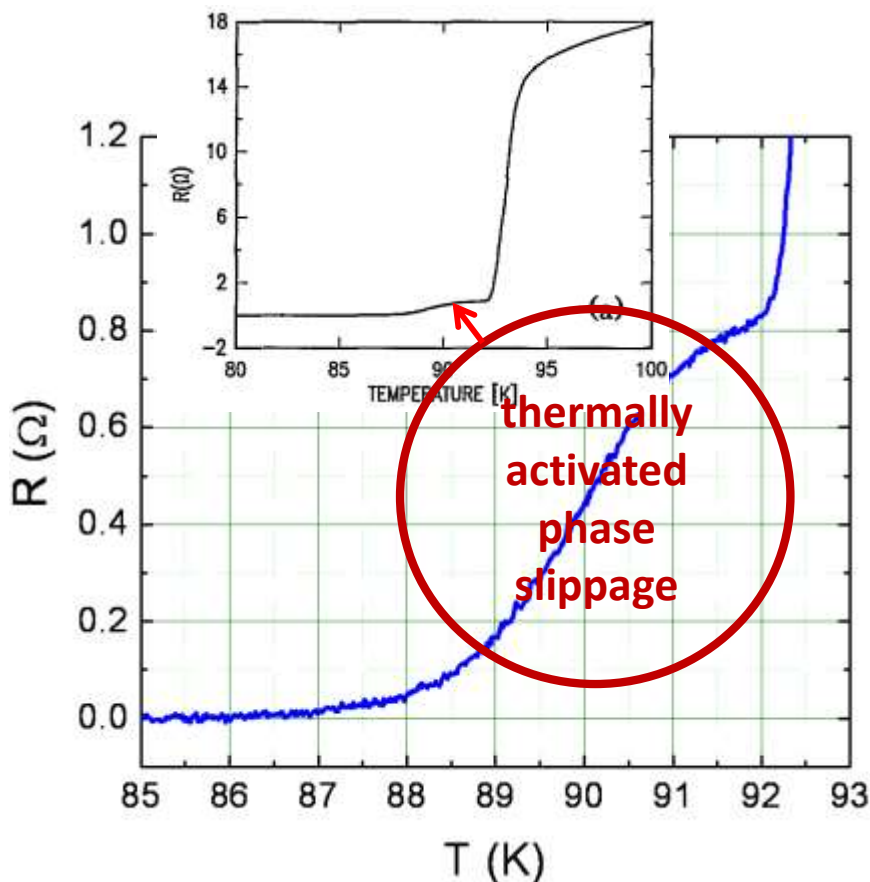
Phys. Rev. Lett. 64, 228 (1990)

Nature 322, 818 (1988)

3.4.2 Additional topic:

Overdamped junctions - The Ambegaokar-Halperin theory

Overdamped $\text{YBa}_2\text{Cu}_3\text{O}_7$ grain boundary Josephson junction



R. Gross et al., Phys. Rev. Lett. 64, 228 (1990)

3.5 Voltage state of extended Josephson junctions

So far

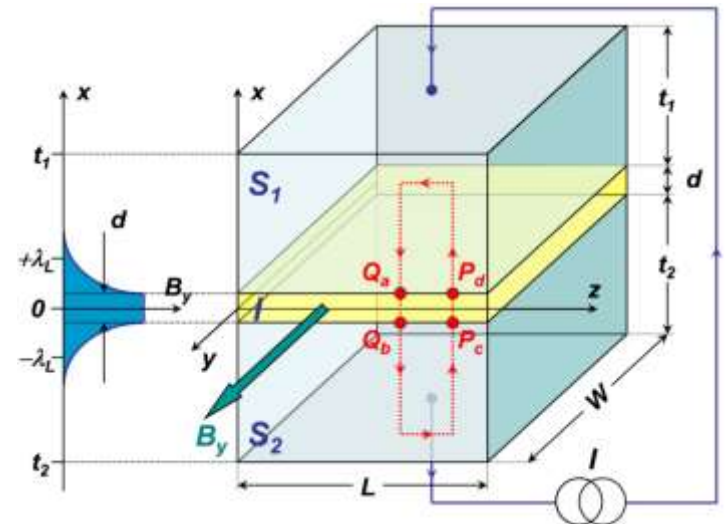
- Junction treated as lumped element circuit element
- Spatial extension neglected

Spatially extended junctions

- Specific geometry as as in Chapter 2
 - Insulating barrier in yz -plane
 - In-plane B field in y -direction
 - Thick electrodes $\gg \lambda_{L,1,2}$
 - Magnetic thickness $t_B = d + \lambda_{L,1} + \lambda_{L,2}$
 - Bias current in x -direction

→ Phase gradient along z -direction

$$\rightarrow \frac{\partial \varphi(z,t)}{\partial z} = \frac{2\pi}{\Phi_0} t_B B_y(z,t)$$



Expected effects

- Voltage state → E -field and time-dependence become important
- Short junction and long junction case

3.5.1 Negligible Screening Effects

Short junctions ($L \ll \lambda_J$) - neglecting self-fields

→ $B = B^{ex}$

→ Junction voltage $V =$ Applied voltage V_0

→ Gauge invariant phase difference:

$$\frac{\partial \varphi}{\partial t} = \frac{2e}{\hbar} V_0 = \omega_0$$

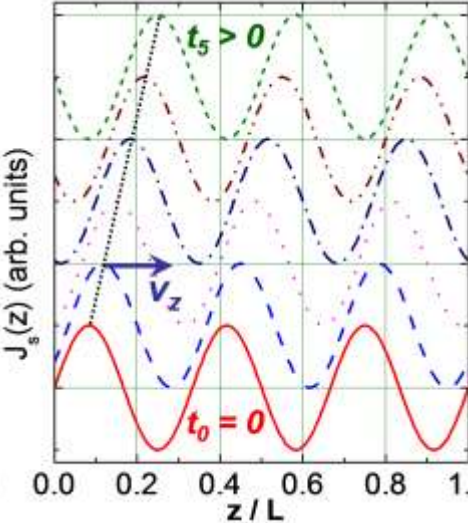
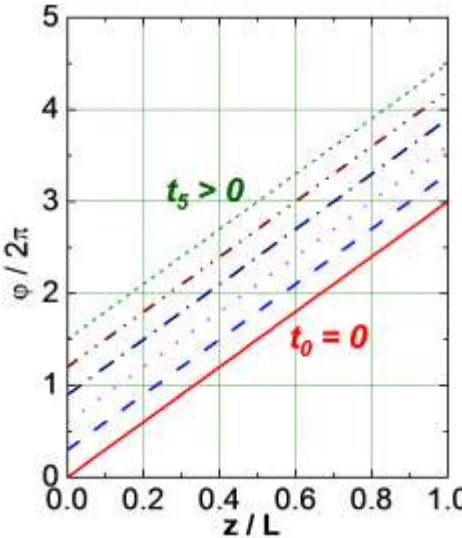
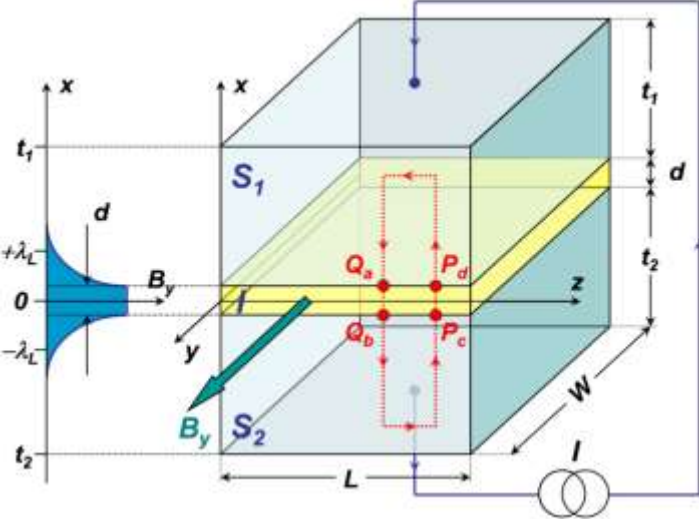
$$\frac{\partial \varphi(z, t)}{\partial z} = \frac{2\pi}{\Phi_0} t_B B_y(z, t)$$

$$\Rightarrow \varphi(z, t) = \varphi_0 + \omega_0 t + \frac{2\pi}{\Phi_0} B_y t_B \cdot z = \varphi_0 + \omega_0 t + k \cdot z$$

$$\Rightarrow J_s(z, t) = J_c \sin(\omega_0 t + k \cdot z + \varphi_0)$$

→ Josephson vortices moving in z-direction with velocity

$$v_z = \frac{\omega_0}{k} = \frac{V_0}{B_y t_B}$$



3.5.2 The time dependent Sine-Gordon equation

Long junctions ($L \gg \lambda_J$)

- Effect of Josephson currents has to be taken into account
- Magnetic flux density = External + Self-generated field

with $\mathbf{B} = \mu_0 \mathbf{H}$ and $\mathbf{D} = \epsilon_0 \mathbf{E}$:
$$\nabla \times \mathbf{B} = \mu_0 \mathbf{J} + \epsilon \epsilon_0 \mu_0 \frac{\partial \mathbf{E}}{\partial t}$$

in contrast to static case,
now $\partial \mathbf{E} / \partial t \neq 0$

consider 1D junction extending in z-direction, $B = B_y$, current flow in x-direction

$$\begin{aligned} \frac{\partial B_y(z, t)}{\partial z} &= -\mu_0 J_x(z, t) - \epsilon \epsilon_0 \mu_0 \frac{\partial E_x(z, t)}{\partial t} \\ \Rightarrow \frac{\partial^2 \varphi(z, t)}{\partial z^2} &= -\frac{2\pi}{\Phi_0} t_B \left\{ \mu_0 J_x(z, t) + \epsilon \epsilon_0 \mu_0 \frac{\partial E_x(z, t)}{\partial t} \right\} \end{aligned}$$

$$\frac{\partial \varphi(z, t)}{\partial z} = \frac{2\pi}{\Phi_0} t_B B_y(z, t)$$

with $E_x = -V/d$, $J_x = -J_c \sin \varphi$ and $\partial \varphi / \partial t = 2\pi V / \Phi_0$:

$$\frac{\partial E_x}{\partial t} = \frac{\partial^2 \varphi}{\partial t^2} \frac{\Phi_0}{2\pi d}(z, t)$$

$$\frac{\partial^2 \varphi(z, t)}{\partial z^2} = \frac{2\pi t_B \mu_0 J_c}{\Phi_0} \sin \varphi(z, t) + \frac{\epsilon \epsilon_0 \mu_0 t_B}{d} \frac{\partial^2 \varphi(z, t)}{\partial t^2}$$

$$\lambda_J \equiv \sqrt{\frac{\Phi_0}{2\pi \mu_0 t_B J_c}}$$

(Josephson penetration depth)

$$\bar{c} = \sqrt{\frac{d}{\epsilon \epsilon_0 \mu_0 t_B}}$$

(propagation velocity)

3.5.2 The time dependent Sine-Gordon equation

$$\Rightarrow \frac{\partial^2 \varphi(z, t)}{\partial z^2} - \frac{1}{\bar{c}^2} \frac{\partial^2 \varphi(z, t)}{\partial t^2} - \frac{1}{\lambda_J^2} \sin \varphi(z, t) = 0$$

Time dependent
Sine-Gordon equation

with the **Swihart velocity**

$$\bar{c} = \sqrt{\frac{d}{\epsilon \epsilon_0 \mu_0 t_B}} = \frac{1}{\sqrt{\epsilon_0 \mu_0}} \sqrt{\frac{d}{\epsilon(2\lambda_L + d)}} = c \sqrt{\frac{1}{\epsilon(1 + 2\lambda_L/d)}}$$

$$\lambda_J \equiv \sqrt{\frac{\Phi_0}{2\pi \mu_0 t_B J_c}}$$

\bar{c} = velocity of TEM mode in the **junction transmission line**

Example: $\epsilon \simeq 5 - 10$, $\frac{2\lambda_L}{d} \simeq 50 - 100 \rightarrow \bar{c} \simeq 0.1c$

→ Reduced wavelength

→ For $f = 10$ GHz → Free space: 3 cm, in junction: 1 mm

Other form of time-dependent Sine-Gordon equation

$$\lambda_J^2 \frac{\partial^2 \varphi(z, t)}{\partial z^2} - \frac{4\pi^2}{\omega_p^2} \frac{\partial^2 \varphi(z, t)}{\partial t^2} - \sin \varphi(z, t) = 0$$

$$\omega_p^2 = 2el_c/\hbar C \quad C/A_i = \epsilon \epsilon_0/d \quad I_c/A_i = J_c \quad c^2 = 1/\epsilon_0 \mu_0 \quad \Rightarrow \omega_p/2\pi = \bar{c}/\lambda_J$$

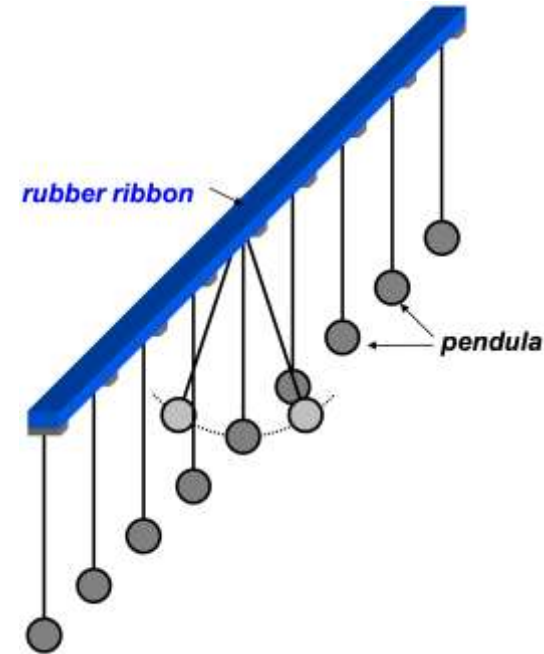
3.5.2 The time dependent Sine-Gordon equation

Time-dependent Sine-Gordon equation:

$$\lambda_J^2 \frac{\partial^2 \varphi(z, t)}{\partial z^2} - \frac{4\pi^2}{\omega_p^2} \frac{\partial^2 \varphi(z, t)}{\partial t^2} - \sin \varphi(z, t) = 0$$

Mechanical analogue

- Chain of mechanical pendula attached to a **twistable rubber ribbon**
- Restoring torque $\lambda_J^2 \frac{\partial^2 \varphi}{\partial z^2}$
- Short junction w/o magnetic field
 - $\partial^2 \varphi / \partial z^2 = 0$
 - Rigid connection of pendula
 - Corresponds to single pendulum



3.5.3 Solutions of the time dependent SG equation

Simple case

→ 1D junction ($W \ll \lambda_J$), short and long junctions

Short junctions ($L \ll \lambda_J$) @ low damping

→ Neglect z-variation of φ

$$\frac{\partial^2 \varphi(z, t)}{\partial t^2} + \frac{\omega_p^2}{4\pi^2} \sin \varphi(z, t) = 0$$

→ Equivalent to RCSJ model for $G_N = 0, I = 0$

Small amplitudes → **Plasma oscillations**

(Oscillation of φ around minimum of washboard potential)

$$\lambda_J^2 \frac{\partial^2 \varphi(z, t)}{\partial z^2} - \frac{4\pi^2}{\omega_p^2} \frac{\partial^2 \varphi(z, t)}{\partial t^2} - \sin \varphi(z, t) = 0$$

$$C/A_i = \epsilon\epsilon_0/d$$

$$I_c/A_i = J_c$$

Long junctions ($L \gg \lambda_J$)

→ Solution for infinitely long junction → **Soliton** or **fluxon**

$$\varphi(z, t) = 4 \arctan \left\{ \exp \left(\pm \frac{\frac{z-z_0}{\lambda_J} - \frac{v_z}{c} t}{\sqrt{1 - \left(\frac{v_z}{c}\right)^2}} \right) \right\}$$

$\varphi = \pi$ at $z = z_0 + v_z t$
 goes from 0 to 2π for $-\infty \rightarrow z \rightarrow \infty$
 → Fluxon (antifluxon: $\infty \rightarrow z \rightarrow -\infty$)

3.5.3 Solutions of the time dependent SG equation

$\varphi = \pi$ at $z = z_0 + v_z t$
 goes from 0 to 2π for $-\infty \rightarrow z \rightarrow \infty$
 → Fluxon (antifluxon: $\infty \rightarrow z \rightarrow -\infty$)

Pendulum analog
 → Local 360° twist of rubber ribbon

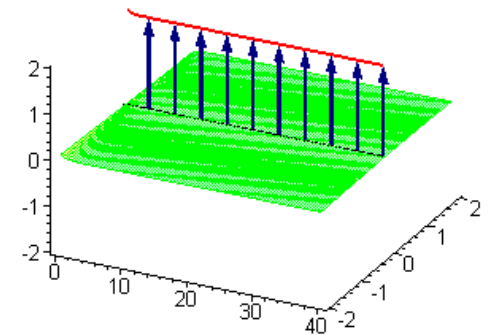
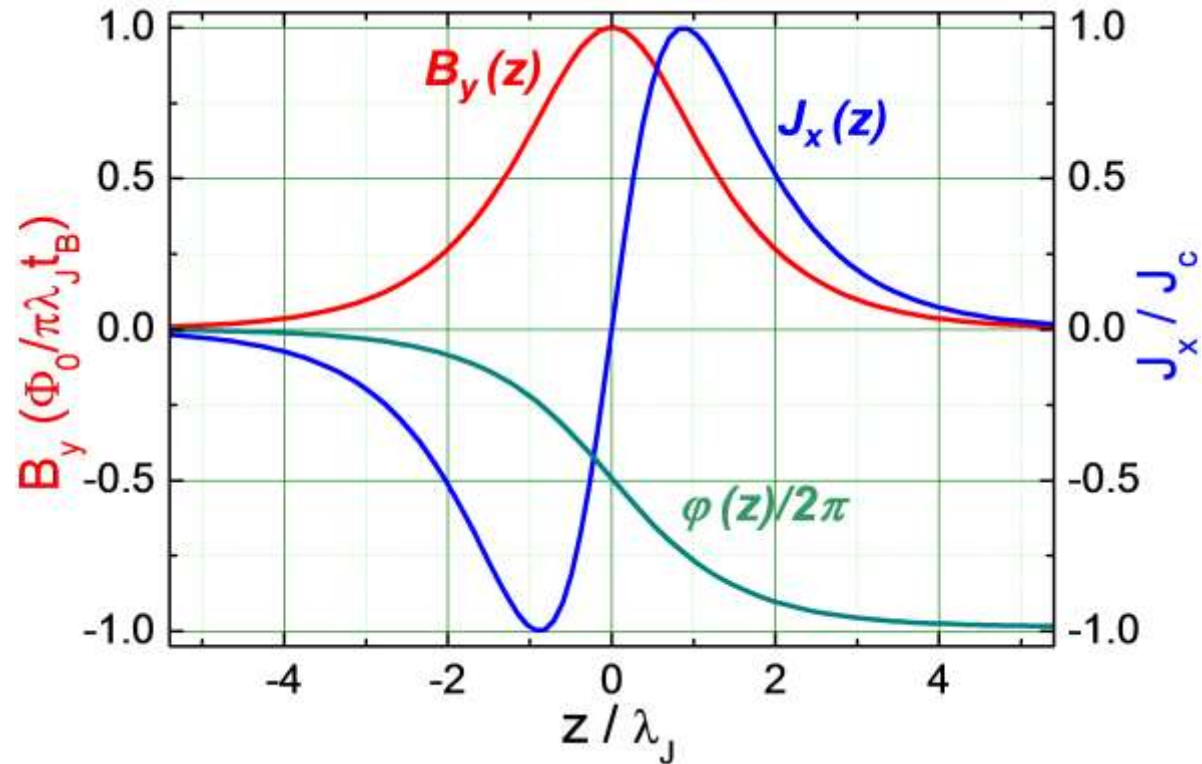
Applied current
 → Lorentz force → Motion of phase twist (fluxon)

Fluxon as particle → Lorentz contraction for $v_z \rightarrow \bar{c}$

Local change of phase difference → Voltage

→ Moving fluxon = Voltage pulse

Other solutions: Fluxon-fluxon collisions, breathers, bound states,...



3.5.3 Solutions of the time dependent SG equation

Josephson plasma waves

Linearized Sine-Gordon equation

$$\varphi(z, t) = \varphi_0(z) + \varphi_1(z, t)$$

$$\sin(\alpha + \beta) = \sin \alpha \cos \beta + \cos \alpha \sin \beta$$

φ_1 = Small deviation

→ Approximation

$$\sin \varphi \simeq \sin \varphi_0 + \varphi_1 \cos \varphi_0$$

Substitution (keeping only linear terms):

$$\frac{\partial^2 \varphi_0}{\partial z^2} + \frac{\partial^2 \varphi_1(z, t)}{\partial z^2} - \frac{1}{c^2} \frac{\partial^2 \varphi_1(z, t)}{\partial t^2} - \frac{1}{\lambda_J^2} \sin \varphi_0 - \frac{1}{\lambda_J^2} \cos \varphi_0 \varphi_1(z, t) = 0$$

φ_0 solves time independent SGE $\frac{\partial^2 \varphi_0}{\partial z^2} = \lambda_J^{-2} \sin \varphi_0$

$$\frac{\partial^2 \varphi_1(z, t)}{\partial z^2} - \frac{1}{c^2} \frac{\partial^2 \varphi_1(z, t)}{\partial t^2} - \frac{1}{\lambda_J^2} \cos \varphi_0 \varphi_1(z, t) = 0$$

φ_0 slowly varying
→ $\varphi_0 \approx \text{const.}$

3.5.3 Solutions of the time dependent SG equation

Solution: $\varphi_1(z, t) = \exp(-i[kz - \omega t])$ (small amplitude plasma waves)

Dispersion relation $\omega(k)$: $\omega^2 = \bar{c}^2 k^2 + \omega_{p,J}^2$

Josephson plasma frequency $\frac{\omega_{p,J}^2}{4\pi^2} = \frac{\bar{c}^2}{\lambda_J^2} \cos \varphi_0 = \frac{\omega_p^2}{4\pi^2} \cos \varphi_0$

$\omega < \omega_{p,J}$

→ Wave vector k imaginary → No propagating solution

$\omega > \omega_{p,J}$

→ Mode propagation

→ Pendulum analogue → Deflect one pendulum → Relax → Wave like excitation

$\omega = \omega_{p,J}$

→ Infinite wavelength Josephson plasma wave

→ Analogy to plasma frequency in a metal

→ Typically junctions $\omega_{p,J} \simeq 10$ GHz

Plane waves

~~$$\Rightarrow \frac{\partial^2 \varphi(z, t)}{\partial z^2} - \frac{1}{\bar{c}^2} \frac{\partial^2 \varphi(z, t)}{\partial t^2} - \frac{1}{\lambda_J^2} \sin \varphi(z, t) = 0$$~~

For very large λ_J or very small I

→ Neglect $\frac{\sin \varphi}{\lambda_J^2}$ term → Linear wave equation → Plane waves with velocity \bar{c}

3.5.4 Resonance phenomena

Interaction of fluxons or plasma waves with oscillating Josephson current

- Rich variety of interesting resonance phenomena
- Require presence of B^{ex}
- Steps in IVC (junction upconverts dc drive)

Flux-flow steps and Eck peak

For $B^{\text{ex}} > 0$

- **Spatially modulated** Josephson current density **moves** at $v_z = V/B_y t_B$
- Josephson current can excite Josephson plasma waves
- On resonance, em waves couple strongly to Josephson current if $\bar{c} = v_z$

Corresponding junction voltage:

$$V_{\text{Eck}} = \bar{c} B_y t_B = \sqrt{\frac{d}{\epsilon \epsilon_0 \mu_0 t_B}} B_y t_B = \frac{\omega_p}{2\pi} \frac{\lambda_J}{L} B_y t_B L = \frac{\omega_p}{2\pi} \frac{\lambda_J}{L} \Phi_0 \frac{\Phi}{\Phi_0}$$

→ **Eck peak** at frequency: $\omega_{\text{Eck}} = \frac{2e}{\hbar} V_{\text{Eck}} = \omega_p \frac{\lambda_J}{L} \frac{\Phi}{\Phi_0}$

$$\bar{c} = \frac{\omega_p}{2\pi} \lambda_J$$
$$\Phi = B_y t_B L$$

3.5.4 Resonance phenomena

- Traveling current wave only excites traveling em wave of same direction
 - Low damping, short junctions → Em wave is reflected at open end
 - Eck peak only observed in **long junctions at medium damping** when the backward wave is damped

Alternative point of view

- Lorentz force → Josephson vortices move at $v_z = \frac{V}{B_y t_B}$
- Increase driving force → Increase v_z
- Maximum possible speed is $v_z = \bar{c}$
- Further increase of I does not increase V)
- **Flux-flow step** in IVC
- $V_{\text{ffs}} = \bar{c} B_y t_B = \bar{c} \frac{\Phi}{L} = \frac{\omega_p \lambda_J}{2\pi L} \Phi_0 \frac{\Phi}{\Phi_0}$
- Corresponds to Eck voltage

3.5.4 Resonance phenomena

Fiske steps

Standing em waves in junction “cavity” at $\omega_n = 2\pi f_n = 2\pi \frac{\bar{c}}{2L} n = \frac{\pi \bar{c}}{L} n$

→ Fiske steps at voltages

$$V_n = \frac{\hbar}{2e} \omega_n = \Phi_0 \frac{\bar{c}}{2L} n = \frac{\omega_p}{2\pi} \frac{\lambda_J}{L} \Phi_0 \frac{n}{2}$$

Interpretation

→ Wave length of Josephson current density is $\frac{2\pi}{k}$

→ Resonance condition $L = \frac{\bar{c}}{2f_n} n = \frac{\lambda}{2} n \Rightarrow kL = n\pi$ or $\Phi = n \frac{\Phi_0}{2}$

where maximum Josephson current of short junction vanishes

→ Standing wave pattern of em wave and Josephson current match

→ Steps in IVC

Influence of dissipation

→ Damping of standing wave pattern by dissipative effects

→ Broadening of Fiske steps

→ Observation only for **small and medium damping**

$\lambda/2$ -cavity

→ $\omega_n = (n\pi v_{ph})/L$

v_{ph} = Phase velocity

for $L \gg 100 \mu\text{m}$

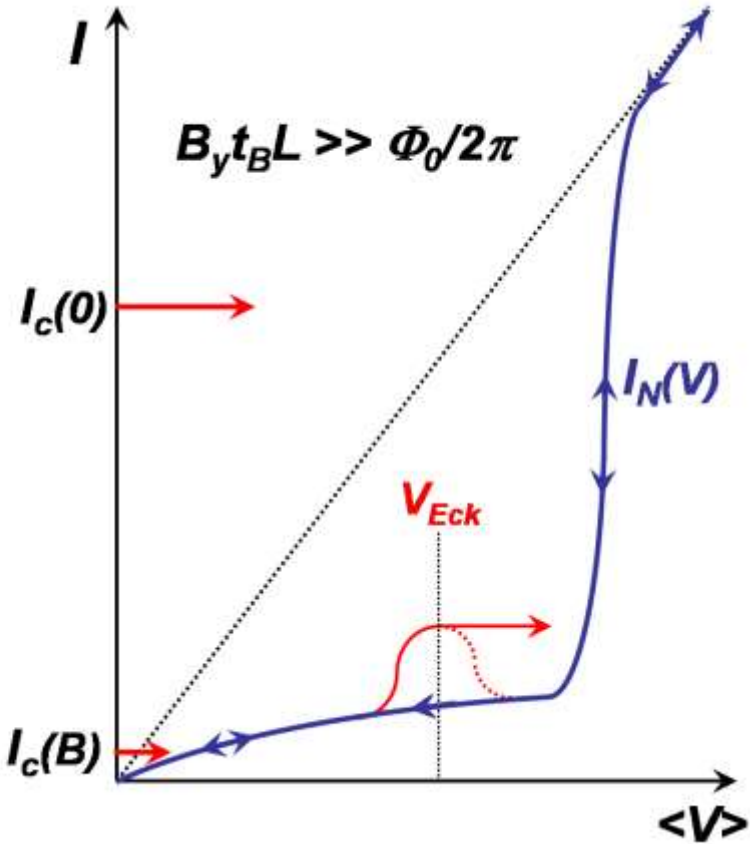
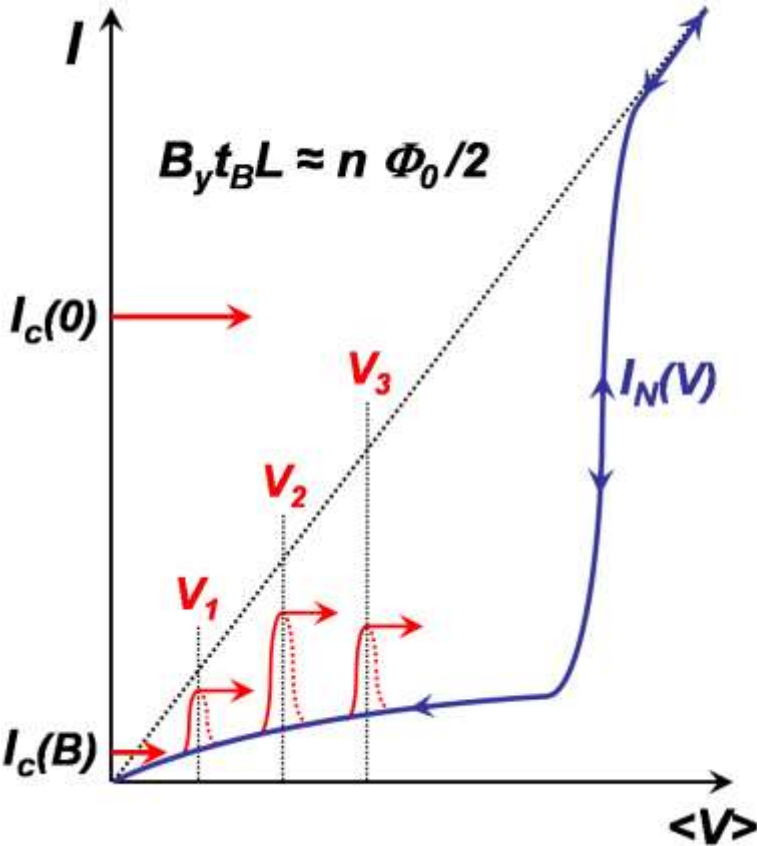
first Fiske step $\gg 10 \text{ GHz}$

(few 10s of μV)

3.5.4 Resonance phenomena

Fiske steps at small damping and/or small magnetic field

Eck peak at medium damping and/or medium magnetic field



For $V \neq V_{Eck}$ and $V \neq V_n \rightarrow \langle I_s \rangle = \langle I_c \sin(\omega_0 t + kz + \varphi_0) \rangle \approx 0 \rightarrow I = I_N(V) = V/R_N(V)$

R. Gross, A. Marx, F. Deppe, and K. Fedorov © Walther-Meißner-Institut (2001 - 2020)

3.5.4 Resonance phenomena

Zero field steps

- Motion of trapped flux due to Lorentz force (w/o magnetic field)
- Junction of length L , moving back and forth
- Phase change of 4π in period $T = \frac{2L}{v_z}$
- At large bias currents ($v_z \rightarrow \bar{c}$)

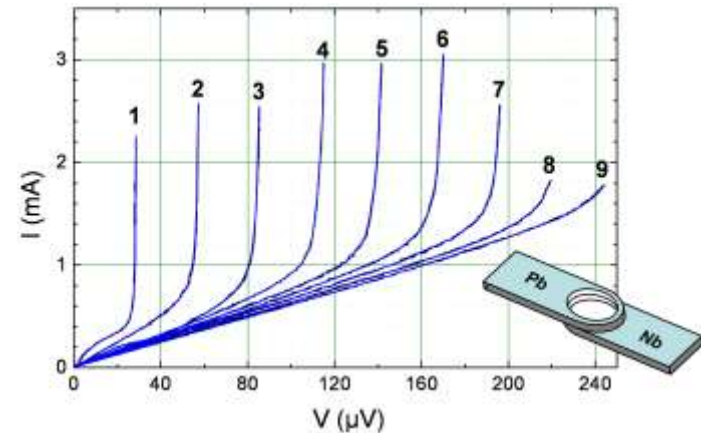
$$V_{zfs} = \dot{\phi} \frac{\hbar}{2e} = \frac{4\pi \hbar}{T} \frac{1}{2e} = \frac{4\pi \hbar}{2L/\bar{c}} \frac{1}{2e} = \frac{h \bar{c}}{2eL} = \frac{\omega_p \lambda_J}{\pi L} \Phi_0$$

For n fluxons

- $V_{n,zfs} = nV_{zfs}$
- $V_{n,zfs} = 2 \times$ Fiske voltage V_n (fluxon has to move back and forth)
- $V_{ffs} = V_{n,zfs}$ for $\Phi = n\Phi_0$ (introduce n fluxons = generate n flux quanta)

Example:

IVCs of **annular Nb/insulator/Pb Josephson junction** containing a different number of trapped fluxons



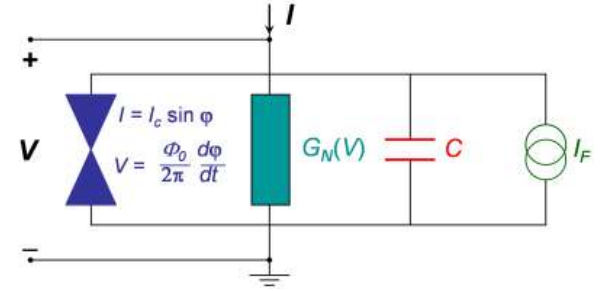
Summary (Voltage state of short junctions)

Voltage state: (Josephson + normal + displacement + fluctuation) current = total current

$$\Rightarrow I = I_c \sin \varphi + G_N(V)V + C \frac{dV}{dt} + I_F$$

$$\frac{d\varphi}{dt} = \frac{2eV}{\hbar}$$

$$\Rightarrow I = I_c \sin \varphi + G_N(V) \frac{\Phi_0}{2\pi} \frac{d\varphi}{dt} + C \frac{\Phi_0}{2\pi} \frac{d^2\varphi}{dt^2} + I_F$$



Equation of motion for phase difference φ :

$$\tau \equiv \frac{t}{\tau_c} = \frac{t}{2eI_c R / \hbar}$$

RCSJ-model ($G_N(V) = \text{const.}$)
$$\beta_C \frac{d^2\varphi}{d\tau^2} + \frac{d\varphi}{d\tau} + \sin \varphi - i - i_F(\tau) = 0$$

Motion of phase particle in the tilted washboard potential $U = E_{J0} [1 - \cos \varphi - (I/I_c)\varphi]$

Equivalent LCR resonator, characteristic frequencies:

$$\omega_p = \sqrt{\frac{1}{L_c C}} = \sqrt{\frac{2eI_c}{\hbar C}} \quad \omega_c = \frac{R}{L_c} = \frac{2eI_c R}{\hbar} \quad \omega_{RC} = \frac{1}{RC}$$

Quality factor: $Q^2 = \beta_C \equiv \frac{2e}{\hbar} I_c R^2 C$ $\beta_C =$ Stewart-McCumber parameter

Summary (Voltage state of short junctions)

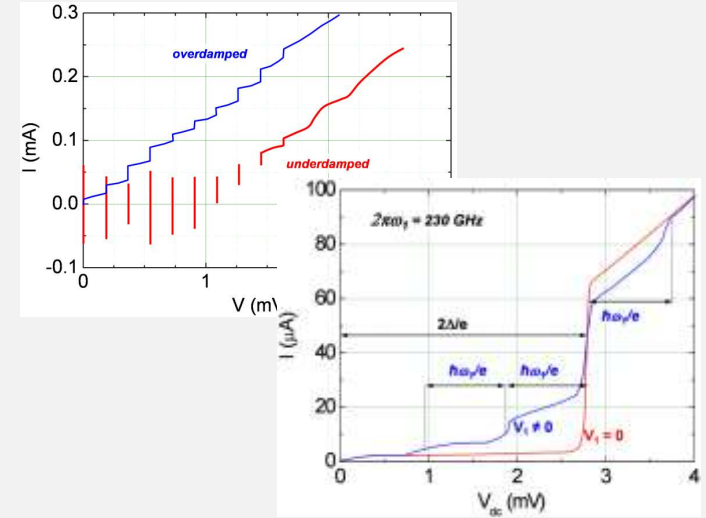
IVC for strong damping and $\beta_C \ll 1$

$$\langle V(t) \rangle = I_c R \sqrt{\left(\frac{I}{I_c}\right)^2 - 1} \quad \text{for } \frac{I}{I_c} > 1$$

Driving with $V(t) = V_{dc} + V_1 \cos \omega_1 t$

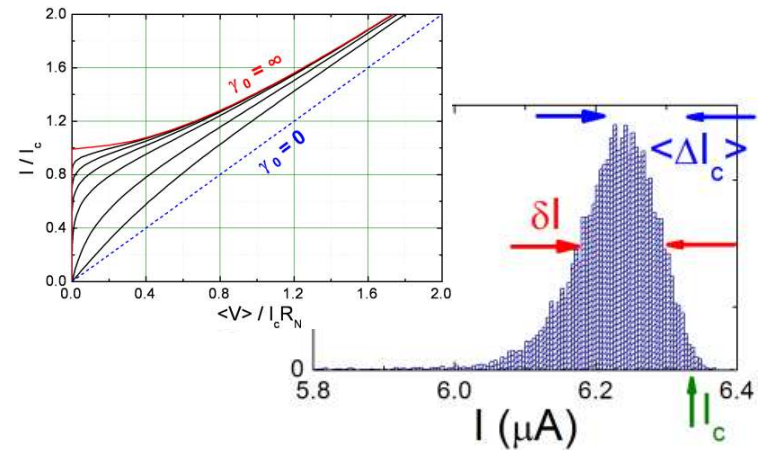
→ **Shapiro steps** at $V_n = n \frac{\Phi_0}{2\pi} \omega_1$
 with amplitudes $|\langle I_S \rangle_n| = I_c \left| \mathcal{J}_n \left(\frac{2\pi V_1}{\Phi_0 \omega_1} \right) \right|$

→ **Photon assisted tunneling**
 Voltage steps at $V_n = n \frac{\Phi_0}{\pi} \omega_1$ due to nonlinear QP resistance



Effect of thermal fluctuations

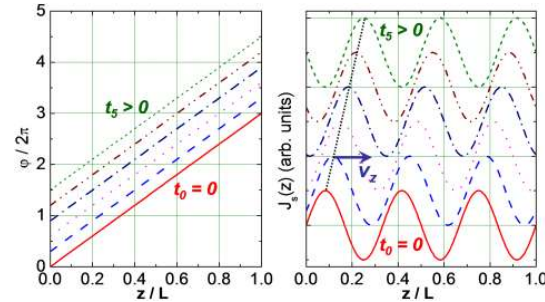
- Phase-slips at rate $\Gamma_{n+1} = \frac{\omega_A}{2\pi} \exp\left(-\frac{U_0}{k_B T}\right)$
- Finite phase-slip resistance R_p even below I_c
- Premature switching



Summary

- voltage state of **extended** junctions w/o self-field:

$$\Rightarrow J_s(z, t) = J_c \sin(\omega_0 t + k \cdot z + \varphi_0)$$



- with self-field: time dependent Sine-Gordon equation

$$\Rightarrow \frac{\partial^2 \varphi(z, t)}{\partial z^2} - \frac{1}{\bar{c}^2} \frac{\partial^2 \varphi(z, t)}{\partial t^2} - \frac{1}{\lambda_J^2} \sin \varphi(z, t) = 0$$

$$\bar{c} = \sqrt{\frac{d}{\epsilon \epsilon_0 \mu_0 t_B}} = c \sqrt{\frac{1}{\epsilon(1 + 2\lambda_L/d)}}$$

characteristic **velocity** of TEM mode in the **junction transmission line**

$$\lambda_J \equiv \sqrt{\frac{\Phi_0}{2\pi \mu_0 t_B J_c}}$$

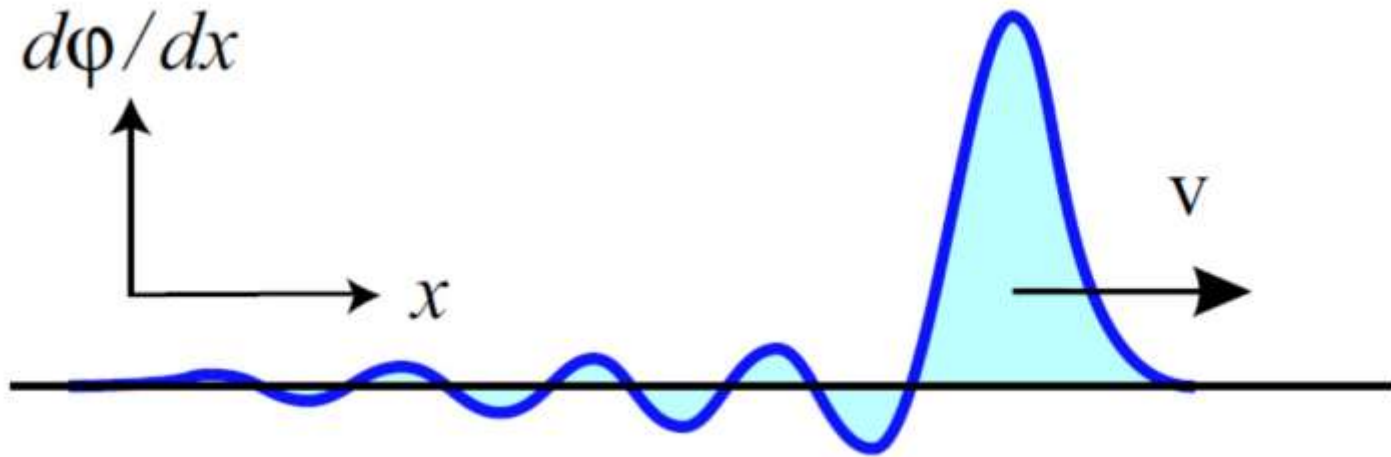
characteristic **screening length**

Prominent solutions: plasma oscillations and solitons

nonlinear interactions of these excitations with Josephson current:

→ **flux-flow steps, Fiske steps, zero-field steps**

Solitons



A **soliton** is a self-reinforcing solitary wave (a wave packet or pulse) that maintains its shape while it travels at constant speed.

Solitons are caused by a cancellation of nonlinear and dispersive effects in the medium.

Solitons

1-d classic soliton in the water canal, discovered in 1834 by J.S. Russel :

Described by Kortweg de Friz (KdF) equation – similar to SG equation.



Solitons

2-d solitons
on the shallow
water surface:

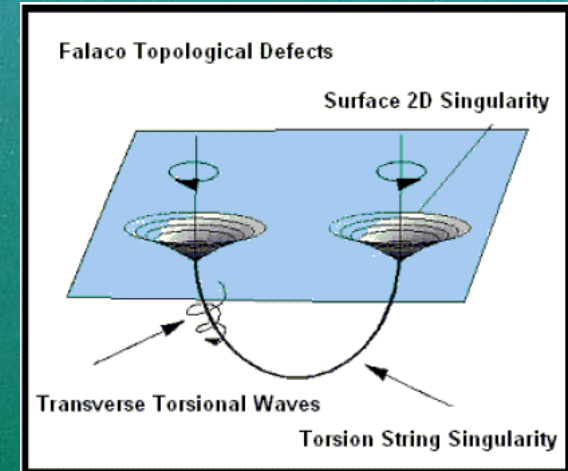
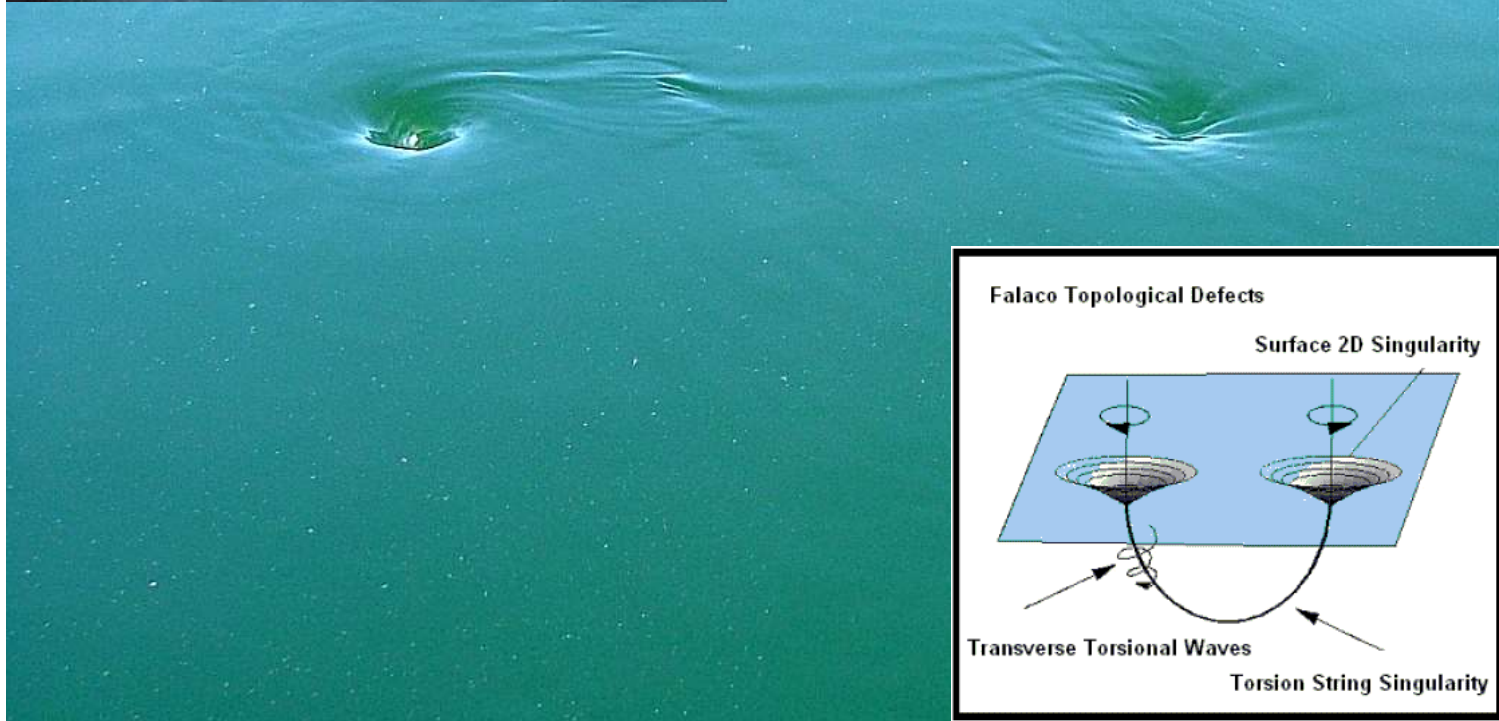
Usually
described
by cnoidal wave
solution of KdF
equation.



Solitons

3-d Falaco soliton in the water pool:

Two vortices are linked together with a turbulent channel deep in the water and moving as the whole.



Solitons

R. Gross, A. Marx, F. Deppe, and K. Fedorov © Walther-Meißner-Institut (2001 - 2020)

“Morning Glory
Clouds”,
Australia,
coastline:

